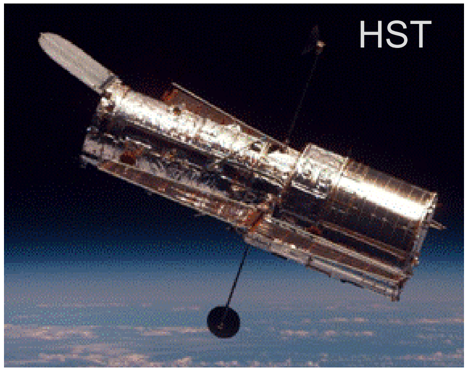
TELEDYNE
IMAGING SENSORS
A Teledyne Technologies Company

Scientific Detectors for Astronomy

1 December 2008

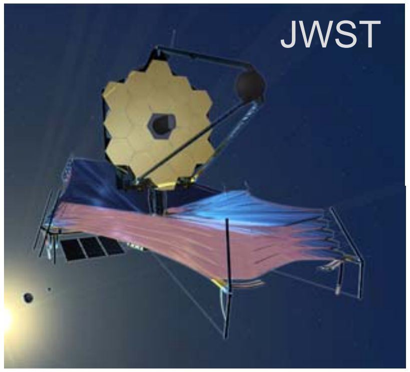
James W. Beletic
Teledyne Imaging Sensors

Teledyne – NASA's Partner in Astronomy



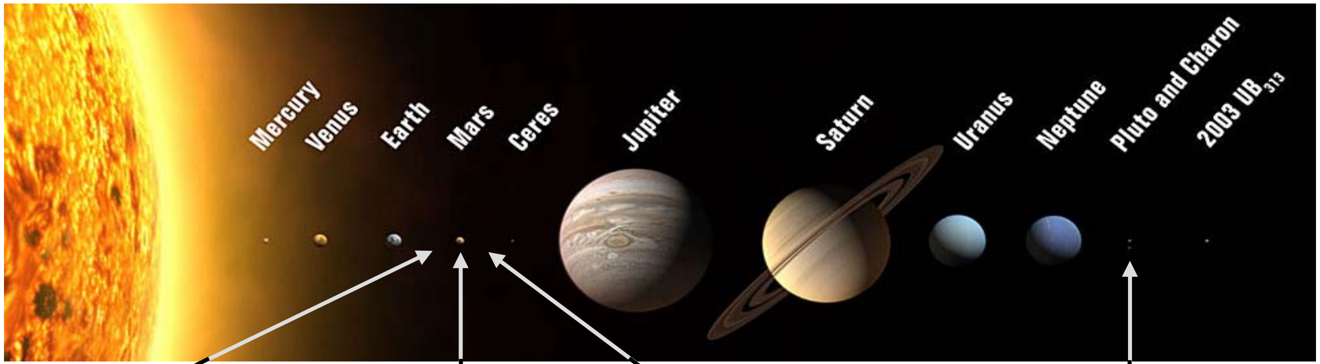
NICMOS, WFC3, ACS Repair

Bands 1 & 2

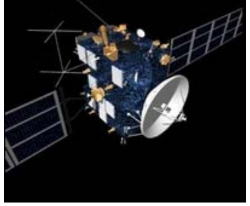


NIRCam, NIRSpec, FGS

Hubble Ultra Deep Field



Rosetta

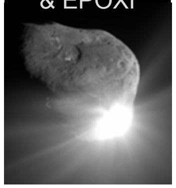


Lander (çiva)

Mars Reconnaissance Orbiter

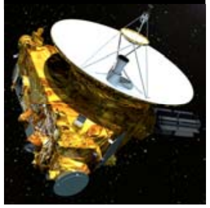
CRISM (Vis & IR)

Deep Impact & EPOXI

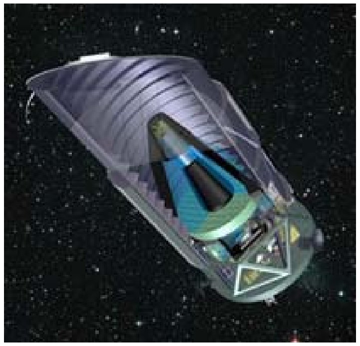


IR spectrograph

New Horizons



IR spectrograph



JDEM

Joint Dark Energy Mission

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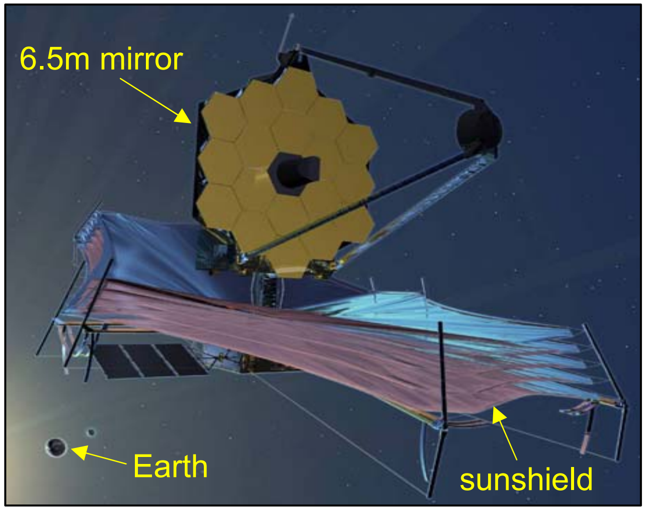
JWST - James Webb Space Telescope

15 Teledyne 2K×2K infrared arrays on board (~63 million pixels)



- International collaboration
- 6.5 meter primary mirror and tennis court size sunshield
- 2013 launch on Ariane 5 rocket
- L2 orbit (1.5 million miles from Earth)

JWST will find the "first light" objects after the Big Bang, and will study how galaxies, stars and planetary systems form

FGS

(Fine Guidance Sensors)

3 individual MWIR 2Kx2K

- **Acquisition and guiding**
- **Images guide stars for telescope stabilization**
- **Canadian Space Agency**

NIRSpec

(Near Infrared Spectrograph)

1x2 mosaic of MWIR 2Kx2K

- **Spectrograph**
- **Measures chemical composition, temperature and velocity**
- **European Space Agency / NASA**

NIRCam

(Near Infrared Camera)

Two 2x2 mosaics of SWIR 2Kx2K

Two individual MWIR 2Kx2K

- **Wide field imager**
- **Studies morphology of objects and structure of the universe**
- **U. Arizona / Lockheed Martin**

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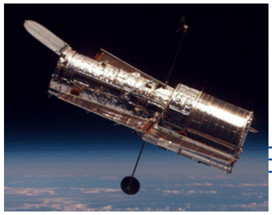
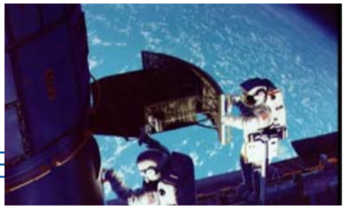
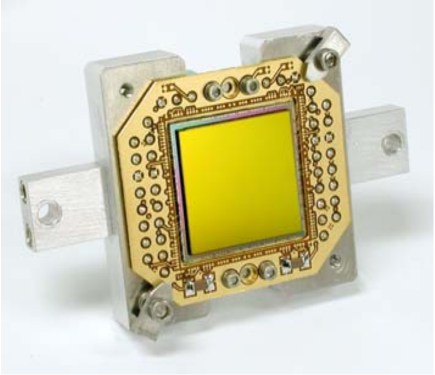
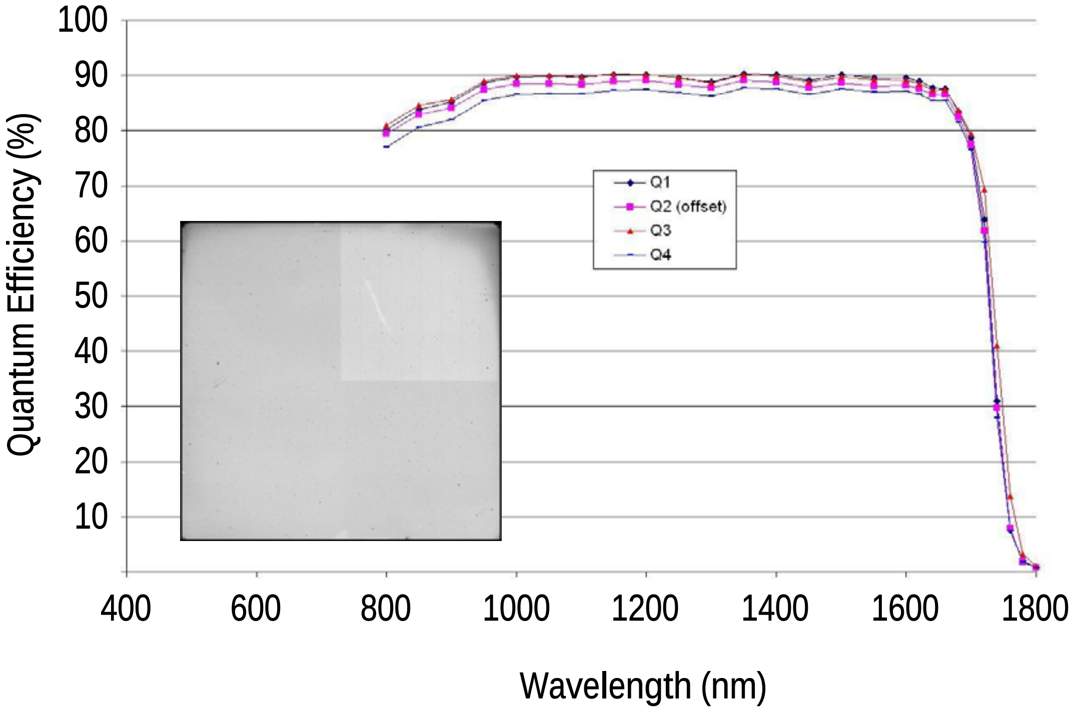


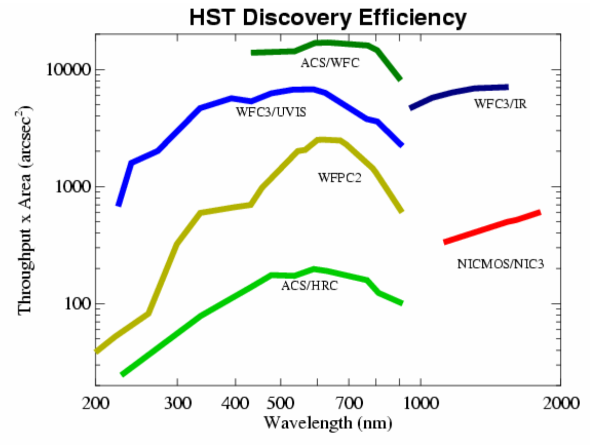
Wide Field Camera 3
Hubble Space Telescope



- **High quality, substrate-removed 1.7 μm HgCdTe arrays delivered to Goddard Space Flight Center**
- **Will be installed in Hubble Space Telescope in 2009**
- **Nearly 30x increase in HST discovery efficiency**







Quantum Efficiency = 85-90%
Dark current (145K) = 0.02 e-/pix/sec
Readout noise = 25 e- (single CDS)

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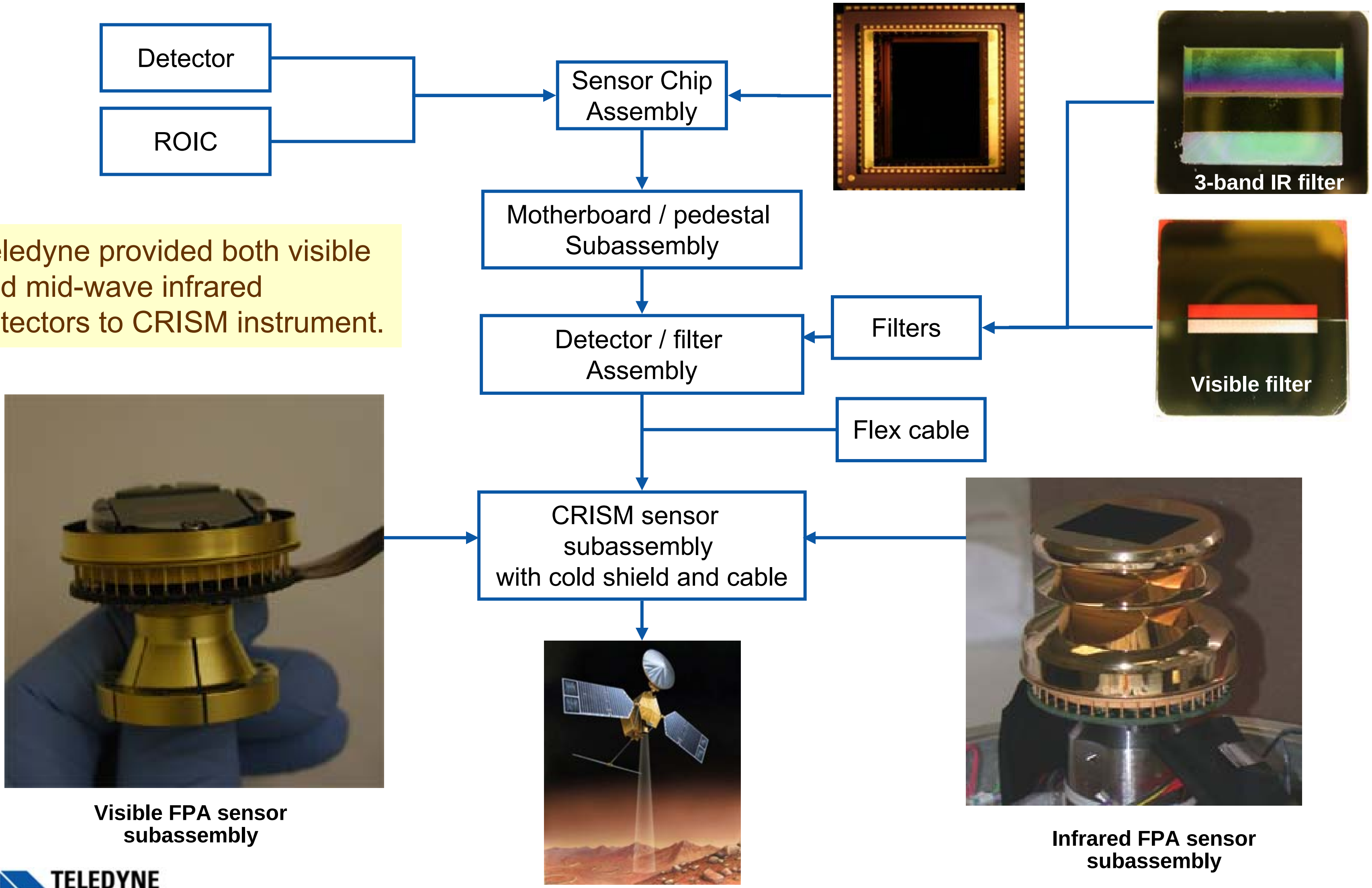
CRISM

Compact Reconnaissance Imaging Spectrometer for Mars

Teledyne provided both visible and mid-wave infrared detectors to CRISM instrument.



Detector

ROIC

Sensor Chip Assembly

Motherboard / pedestal Subassembly

Detector / filter Assembly

Filters

3-band IR filter

Visible filter

Flex cable

CRISM sensor subassembly with cold shield and cable

Visible FPA sensor subassembly

Infrared FPA sensor subassembly

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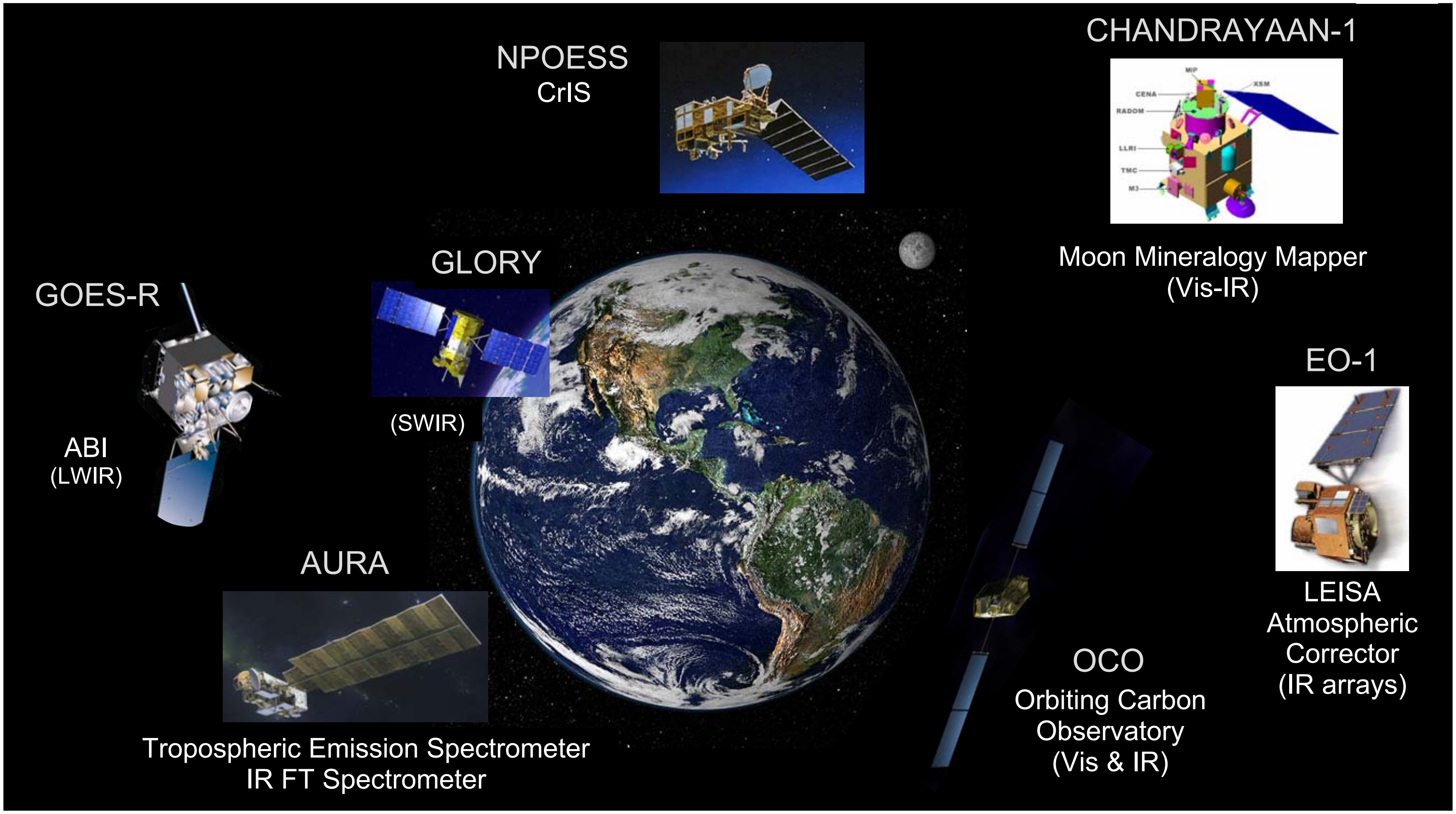
NASA’s and NOAA’s Partner for Earth Observation



NPOESS
CrIS

CHANDRAYAAN-1
Moon Mineralogy Mapper
(Vis-IR)

GOES-R
ABI
(LWIR)

GLORY
(SWIR)

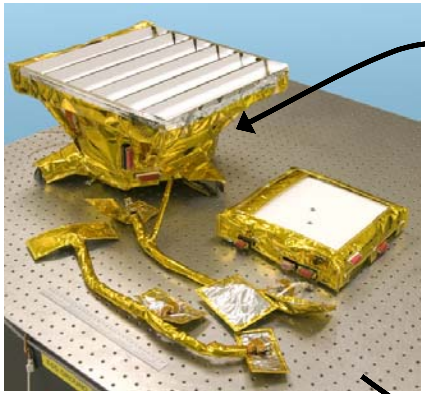
EO-1
LEISA
Atmospheric
Corrector
(IR arrays)

AURA
Tropospheric Emission Spectrometer
IR FT Spectrometer

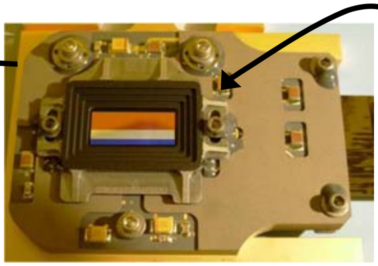
OCO
Orbiting Carbon
Observatory
(Vis & IR)

Visible to 16.5 microns

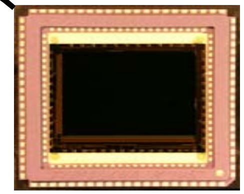
Moon Mineralogy Mapper - Visible / Near Infrared Imaging Spectrometer launched Wednesday, October 22, 2008



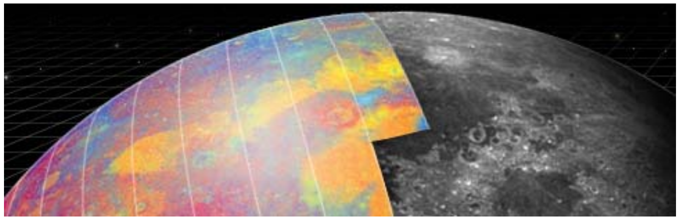
Instrument at JPL before
shipment to India



Focal Plane Assembly



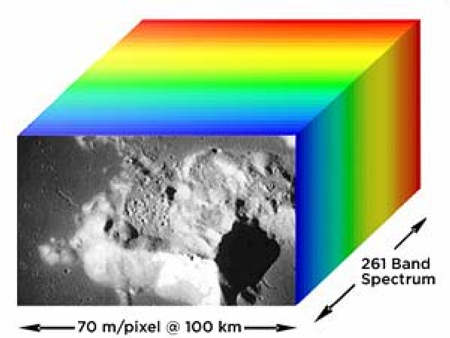
Sensor Chip Assembly



2 year mission will map the entire lunar surface

Teledyne Infrared FPA

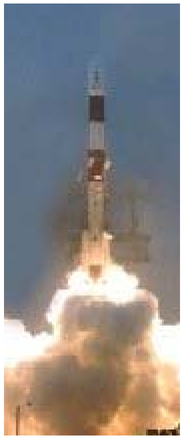
- 640 x 480 pixels (27 µm pitch)
- Substrate-removed HgCdTe (0.4 to 3.0 µm)
- 650,000 e- full well, <100 e- noise
- 100 Hz frame rate (integrate while read)
- < 70 mW power dissipation
- Package includes order sorting filter
- Total FPA mass: 58 grams



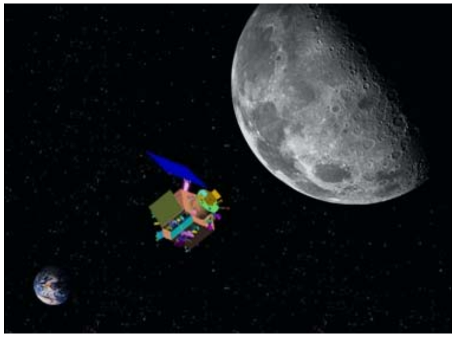
Moon Mineralogy Mapper resolves visible and infrared
to 10 nm spectral resolution, 70 m spatial resolution

Completion of Chandrayaan-1 spacecraft integration
Moon Mineralogy Mapper is white square at end of arrow

Chandrayaan-1 in the
Polar Satellite Launch Vehicle



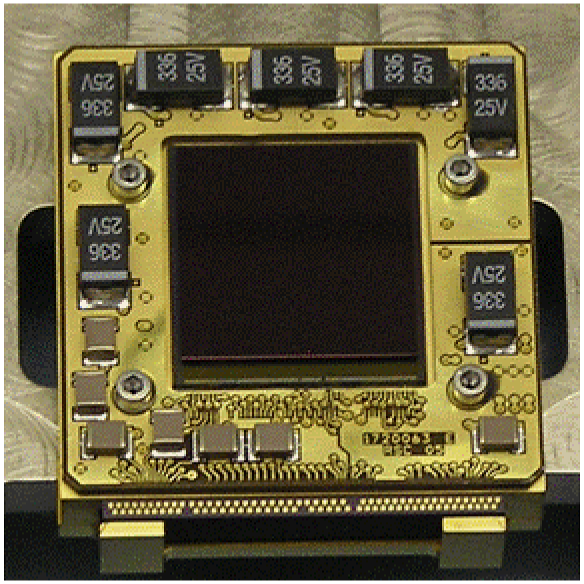
Launch from Satish
Dhawan Space Centre

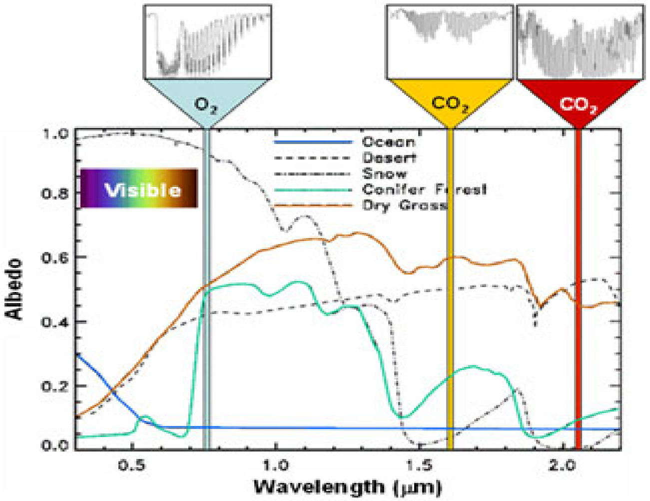


Journey Earth to Moon
100 km altitude lunar orbit

Orbiting Carbon Observatory (OCO)

- The Orbiting Carbon Observatory (OCO) is a NASA mission that will provide:
  - precise, time-dependent global measurements of atmospheric carbon dioxide (CO_2) from an Earth orbiting satellite.
  - distribution of CO_2 over the entire globe, enable more reliable forecasts of future changes and their effect on the Earth's climate.
- The OCO is planned to launch in January 2009 with a planned operational life of 2 years.



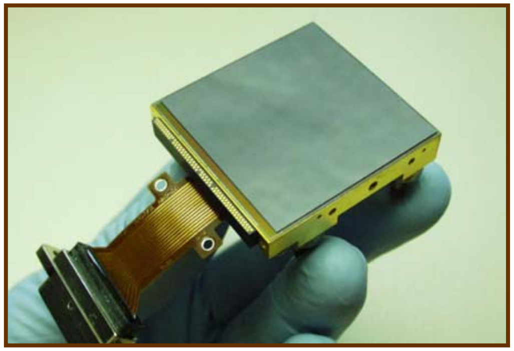


<u>Teledyne Focal Plane Arrays</u>

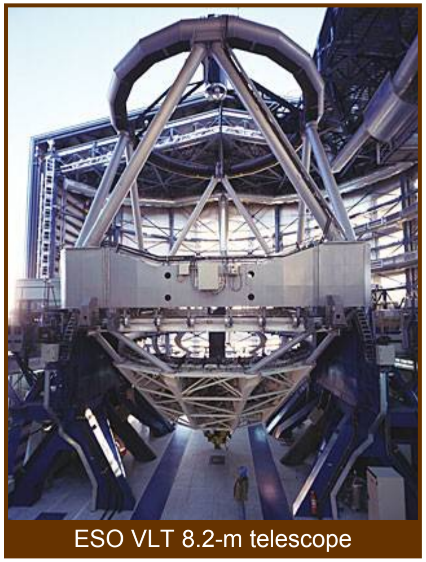
- Three flight FPAs (and flight spares):
  - O_2A band at 0.758-0.772 μm
  - weak CO_2 band at 1.594 -1.619 μm
  - strong CO_2 band at 2.042-2.082 μm
- Hawaii-1RG readout is used for both HyViSI and SWIR FPAs with same mechanical and nearly same electrical interface for all three OCO spectrometers.

Leading Supplier of IR Arrays To Ground-based Astronomy

- H2RG (2048×2048 pixels) is the leading IR FPA in ground-based IR astronomy
- 4096×4096 pixel mosaic commissioned at European Southern Observatory in July 2007
  - 6th mosaic at major telescope, two more mosaics to be commissioned in 2009



ESO Very Large Telescope (VLT) Facility - Chile



ESO VLT 8.2-m telescope

◀ PPLN enables mirrorless OPO

LaserFocusWorld

OCTOBER 2007

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INTERNATIONAL RESOURCE FOR TECHNOLOGY AND APPLICATIONS IN THE GLOBAL PHOTONICS INDUSTRY

Advanced IR arrays give stellar views PAGE 75

▶ Nonpolar GaN lasers: The next new blue

▶ Optical fibers go nano

▶ DFG lasers hit sensing 'sweet spot'

▶ Manufacturers' Product Showcase

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Energy of a photon

Wavelength (μm)	**Energy (eV)**	**Band**
0.3	4.13	UV
0.5	2.48	Vis
0.7	1.77	Vis
1.0	1.24	NIR
2.5	0.50	SWIR
5.0	0.25	MWIR
10.0	0.12	LWIR
20.0	0.06	VLWIR

- Energy of photons is measured in electron-volts (eV)
- eV = energy that an electron gets when it “falls” through a 1 volt field.

An electron-volt (eV) is extremely small

1 eV = $1.6 \cdot 10^{-19}$ J (J = joule)

1 J = N • m = kg • m • sec^{-2} • m

1 kg raised 1 meter = 9.8 J = $6.1 \cdot 10^{19}$ eV

- The energy of a photon is **VERY** small
  - The energy of a SWIR (2.5 μm) photon is 0.5 eV
- Drop a peanut M&M® candy from a height of 5 cm
  - Energy is equal to 6×10^{15} eV (a peanut M&M® is ~2 g)
  - This is equal to 1.2×10^{16} SWIR photons
    - 1 million x 1 million x 12,000
    - The number of photons that will be detected in ~1 million images from the James Webb Space Telescope (JWST)
    - **A 2-inch peanut M&M® drop is about same energy that will be detected during the 5 years operation of the James Webb Space Telescope !**

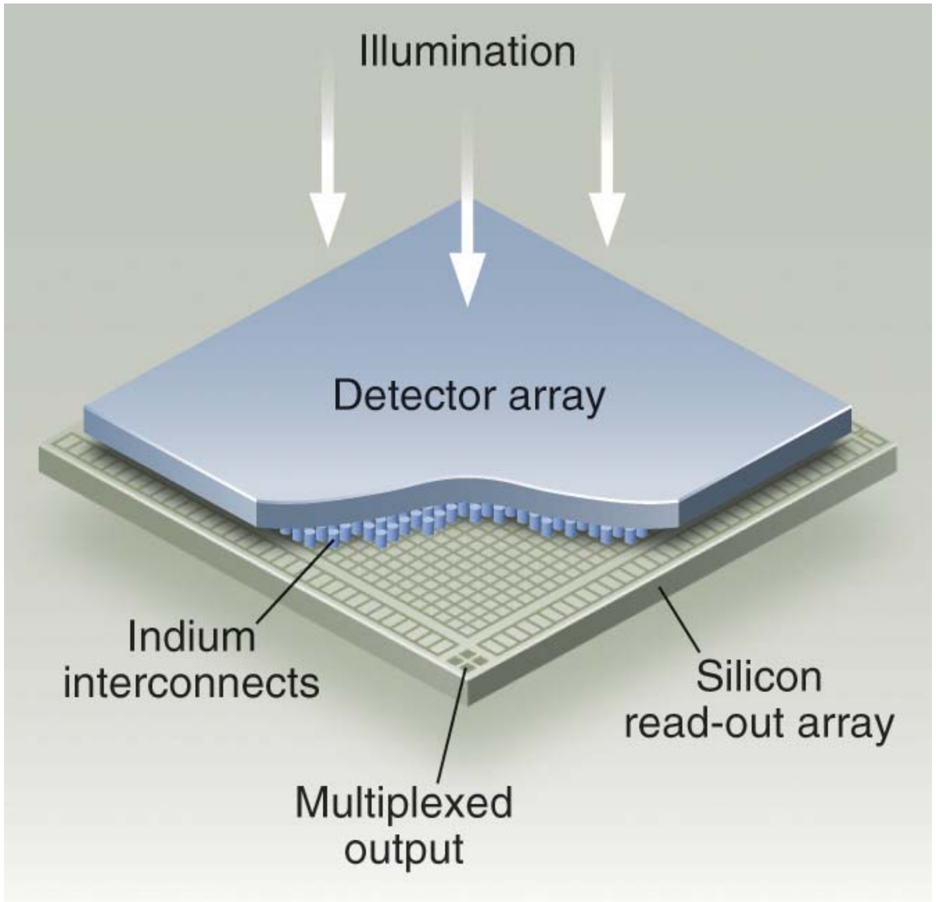
$E = h\nu$

h = Planck constant (6.6310^{-34} Joule•sec)

ν = frequency of light (cycles/sec) = λ/c

www.foxtrot.com

Hybrid CMOS Infrared Imaging Sensors

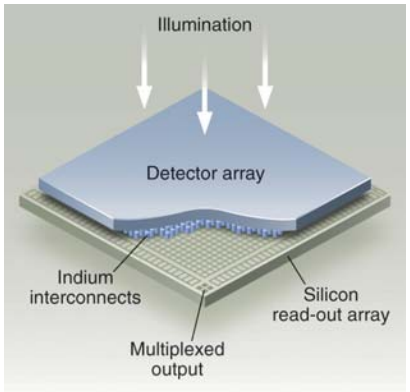


Large, high performance IR arrays

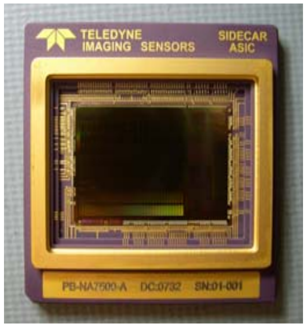
Three Key Technologies

1. Growth and processing of the HgCdTe detector layer
2. Design and fabrication of the CMOS readout integrated circuit (ROIC)
3. Hybridization of the detector layer to the CMOS ROIC

6 Steps of CMOS-based Optical / IR Photon Detection



HYBRID SENSOR
CHIP ASSEMBLY (SCA)



SIDECAR ASIC

Anti-reflection coating
Substrate removal

1. Light into detector

Detector Materials
HgCdTe, Si

2. Charge Generation

Electric Fields in detector
collect electrical charge
p-n junction

3. Charge Collection

Source follower

4. Charge-to-Voltage Conversion

Random access
or full frame read

5. Signal Transfer

SIDECAR ASIC

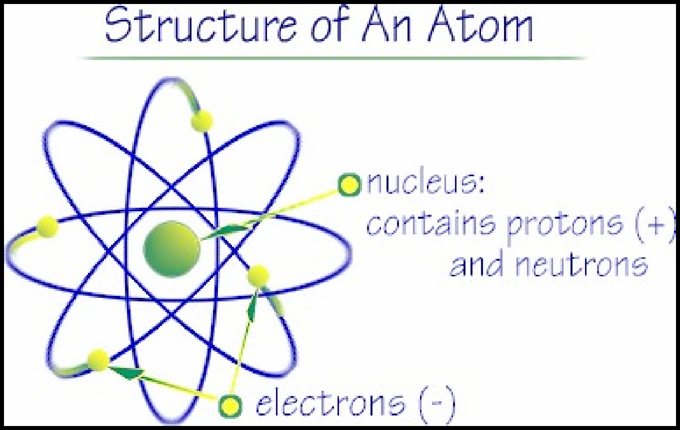
6. Digitization

Quantum Efficiency

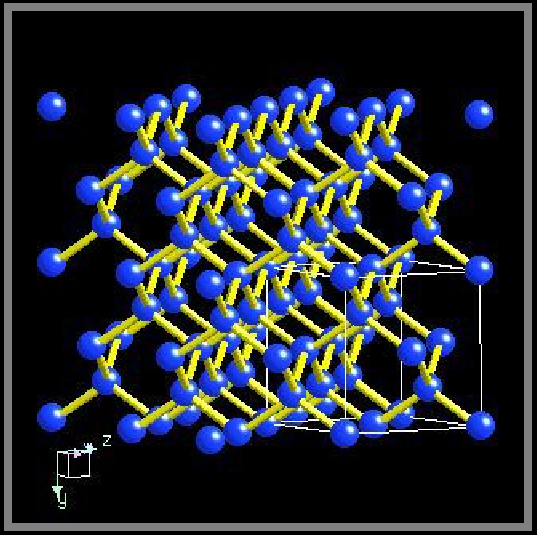
Point Spread Function

Sensitivity

Crystals are excellent detectors of light



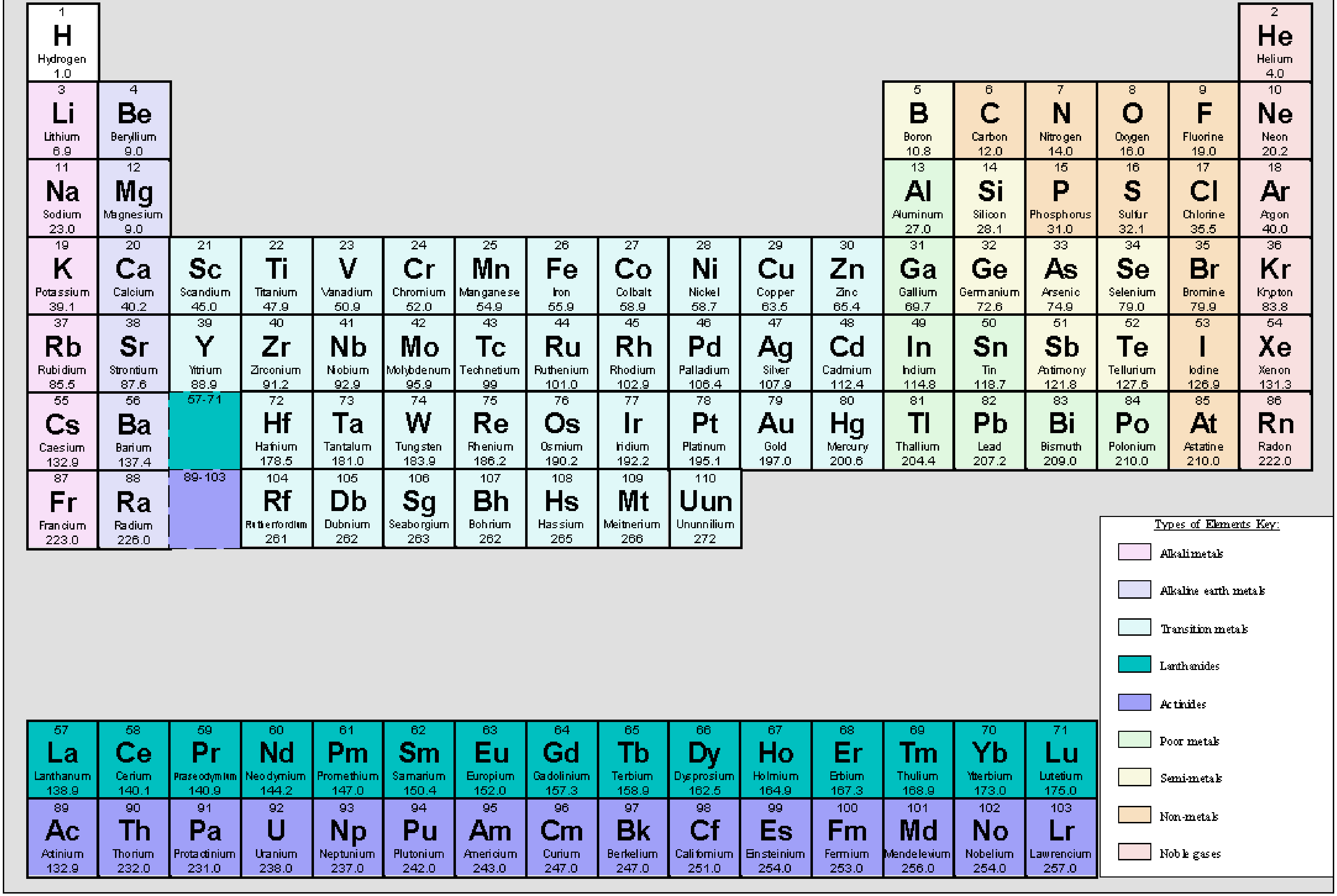
- Simple model of atom
  - Protons (+) and neutrons in the nucleus with electrons orbiting



Silicon crystal lattice

- Electrons are trapped in the crystal lattice
  - by electric field of protons
- Light energy can free an electron from the grip of the protons, allowing the electron to roam about the crystal
  - creates an “electron-hole” pair.
- The photocharge can be collected and amplified, so that light is detected
- The light energy required to free an electron depends on the material.

Periodic Table



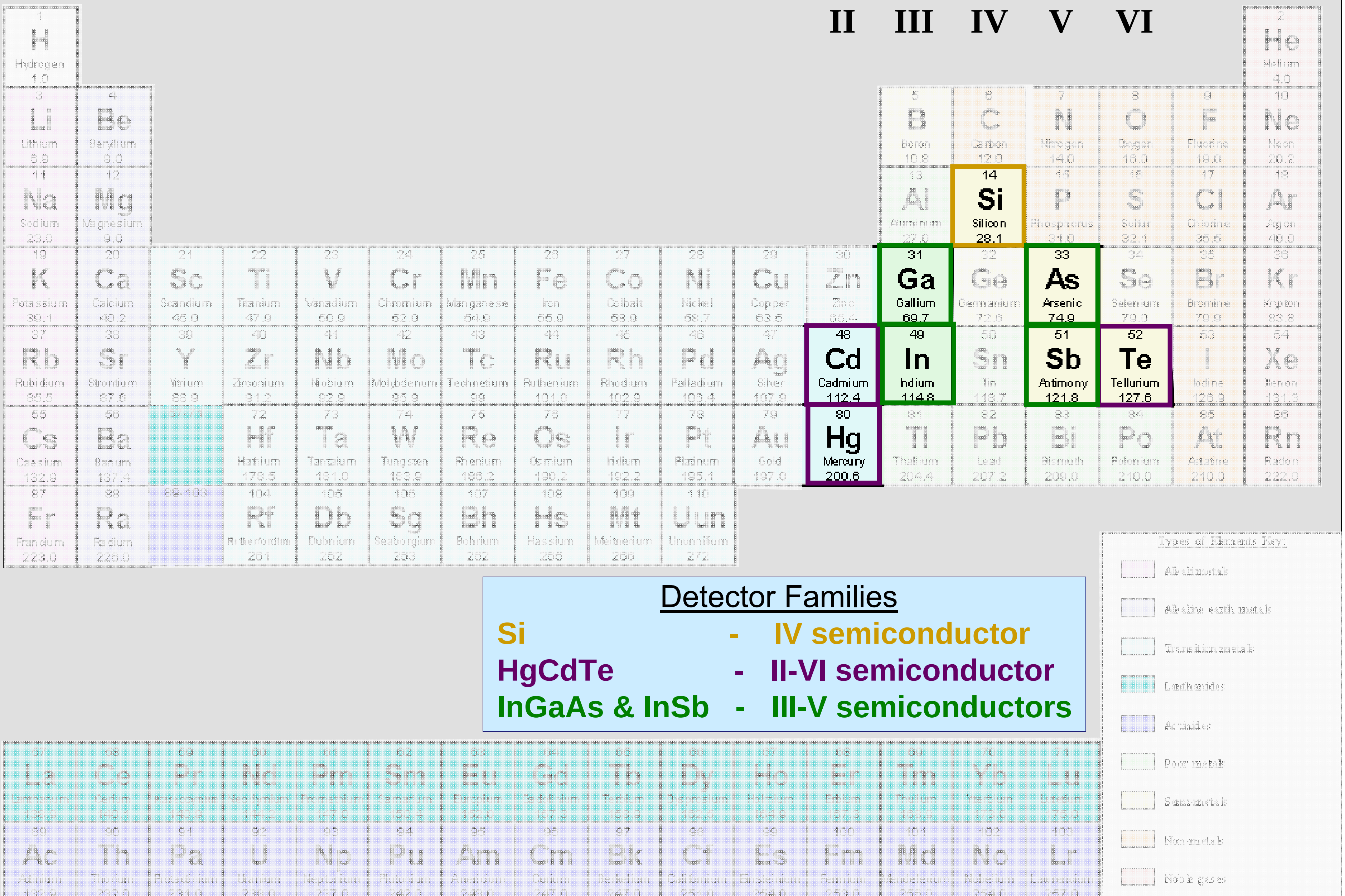
1 H Hydrogen 1.0																	2 He Helium 4.0
3 Li Lithium 6.9	4 Be Beryllium 9.0											5 B Boron 10.8	6 C Carbon 12.0	7 N Nitrogen 14.0	8 O Oxygen 16.0	9 F Fluorine 19.0	10 Ne Neon 20.2
11 Na Sodium 23.0	12 Mg Magnesium 9.0											13 Al Aluminum 27.0	14 Si Silicon 28.1	15 P Phosphorus 31.0	16 S Sulfur 32.1	17 Cl Chlorine 35.5	18 Ar Argon 40.0
19 K Potassium 39.1	20 Ca Calcium 40.2	21 Sc Scandium 45.0	22 Ti Titanium 47.9	23 V Vanadium 50.9	24 Cr Chromium 52.0	25 Mn Manganese 54.9	26 Fe Iron 55.9	27 Co Colbalt 58.9	28 Ni Nickel 58.7	29 Cu Copper 63.5	30 Zn Zinc 65.4	31 Ga Gallium 69.7	32 Ge Germanium 72.6	33 As Arsenic 74.9	34 Se Selenium 79.0	35 Br Bromine 79.9	36 Kr Krypton 83.8
37 Rb Rubidium 85.5	38 Sr Strontium 87.6	39 Y Yttrium 88.9	40 Zr Zirconium 91.2	41 Nb Niobium 92.9	42 Mo Molybdenum 95.9	43 Tc Technetium 99	44 Ru Ruthenium 101.0	45 Rh Rhodium 102.9	46 Pd Palladium 106.4	47 Ag Silver 107.9	48 Cd Cadmium 112.4	49 In Indium 114.8	50 Sn Tin 118.7	51 Sb Antimony 121.8	52 Te Tellurium 127.6	53 I Iodine 126.9	54 Xe Xenon 131.3
55 Cs Caesium 132.9	56 Ba Barium 137.4	57-71	72 Hf Hafnium 178.5	73 Ta Tantalum 181.0	74 W Tungsten 183.9	75 Re Rhenium 186.2	76 Os Osmium 190.2	77 Ir Iridium 192.2	78 Pt Platinum 195.1	79 Au Gold 197.0	80 Hg Mercury 200.6	81 Tl Thallium 204.4	82 Pb Lead 207.2	83 Bi Bismuth 209.0	84 Po Polonium 210.0	85 At Astatine 210.0	86 Rn Radon 222.0
87 Fr Francium 223.0	88 Ra Radium 226.0	89-103	104 Rf Rutherfordium 261	105 Db Dubnium 262	106 Sg Seaborgium 263	107 Bh Bohrium 262	108 Hs Hassium 265	109 Mt Meitnerium 266	110 Uun Ununnilium 272								

57 La Lanthanum 138.9	58 Ce Cerium 140.1	59 Pr Praseodymium 140.9	60 Nd Neodymium 144.2	61 Pm Promethium 147.0	62 Sm Samarium 150.4	63 Eu Europium 152.0	64 Gd Gadolinium 157.3	65 Tb Terbium 158.9	66 Dy Dysprosium 162.5	67 Ho Holmium 164.9	68 Er Erbium 167.3	69 Tm Thulium 168.9	70 Yb Ytterbium 173.0	71 Lu Lutetium 175.0
89 Ac Actinium 132.9	90 Th Thorium 232.0	91 Pa Protactinium 231.0	92 U Uranium 238.0	93 Np Neptunium 237.0	94 Pu Plutonium 242.0	95 Am Americium 243.0	96 Cm Curium 247.0	97 Bk Berkelium 247.0	98 Cf Californium 251.0	99 Es Einsteinium 254.0	100 Fm Fermium 253.0	101 Md Mendelevium 256.0	102 No Nobelium 254.0	103 Lr Lawrencium 257.0

Types of Elements Key:

- ▨ Alkali metals
- ▨ Alkaline earth metals
- ▨ Transition metals
- ▨ Lanthanides
- ▨ Actinides
- ▨ Poor metals
- ▨ Semi-metals
- ▨ Non-metals
- ▨ Noble gases

Periodic Table

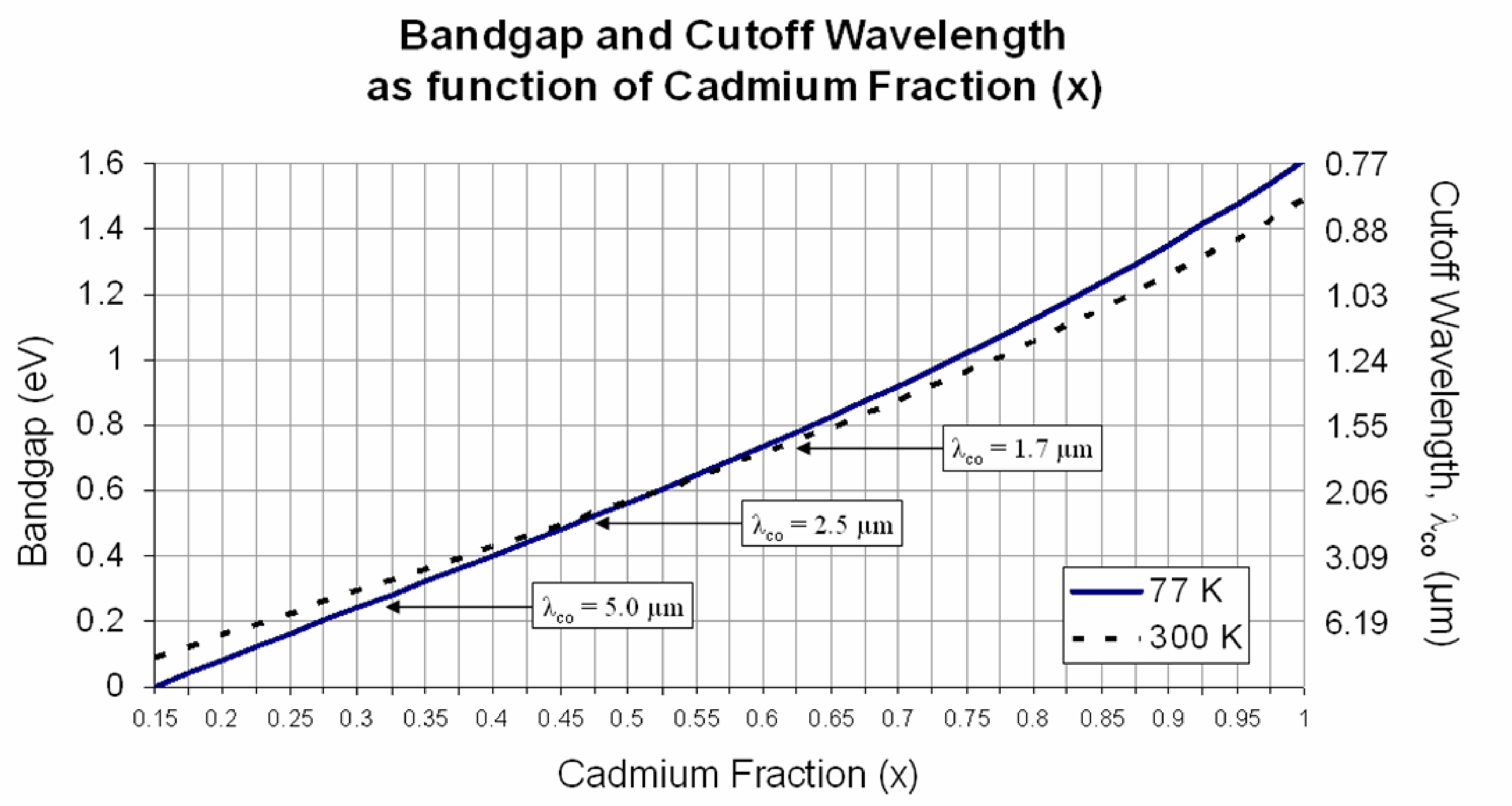


Detector Families

Si - IV semiconductor
HgCdTe - II-VI semiconductor
InGaAs & InSb - III-V semiconductors

Tunable Wavelength: Unique property of HgCdTe

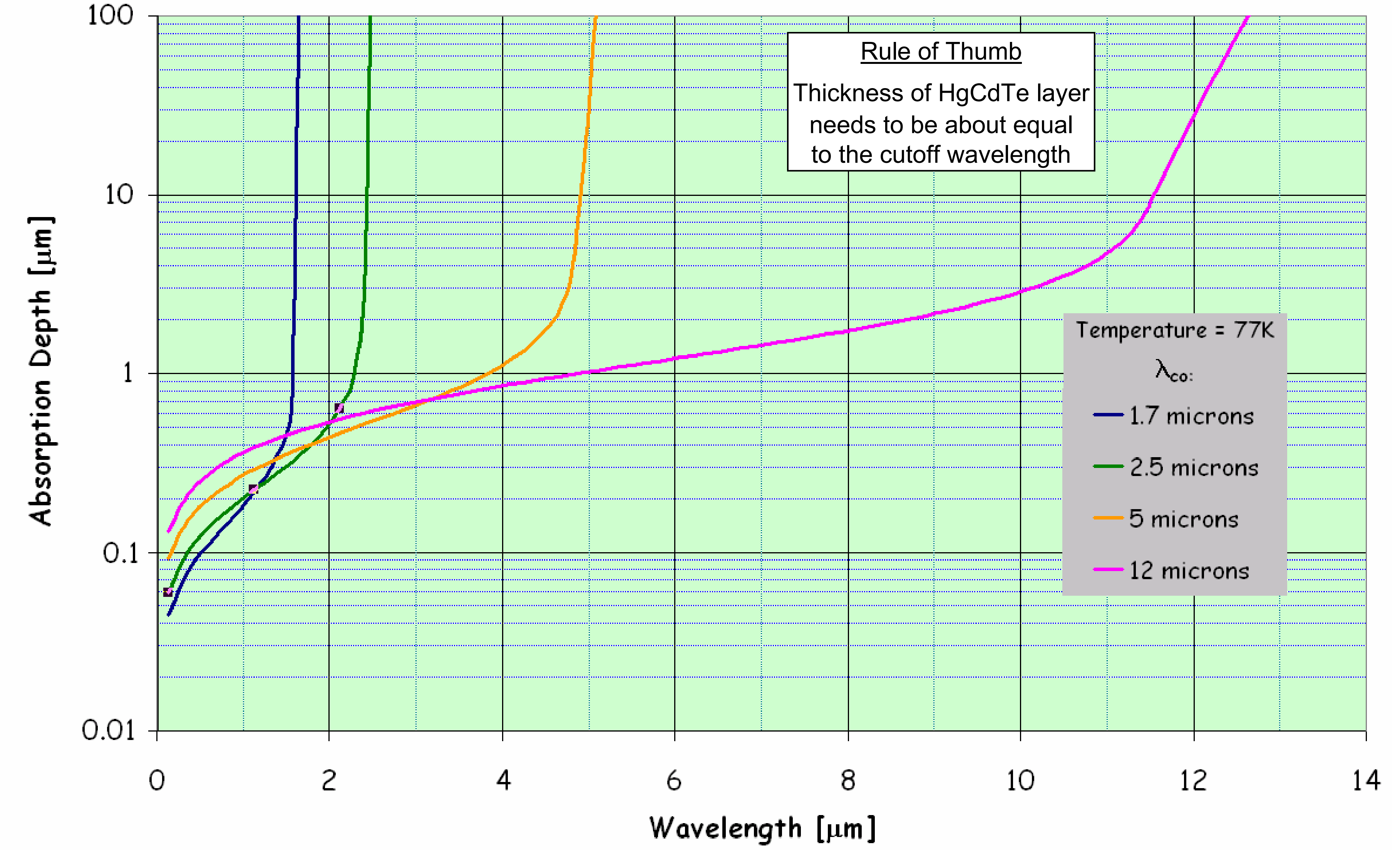
$Hg_{1-x}Cd_xTe$ Modify ratio of Mercury and Cadmium to "tune" the bandgap energy



$$E_g = -0.302 + 1.93x - 0.81x^2 + 0.832x^3 + 5.35\times10^{-4}T(1-2x)$$

G. L. Hansen, J. L. Schmidt, T. N. Casselman, J. Appl. Phys. 53(10), 1982, p. 7099

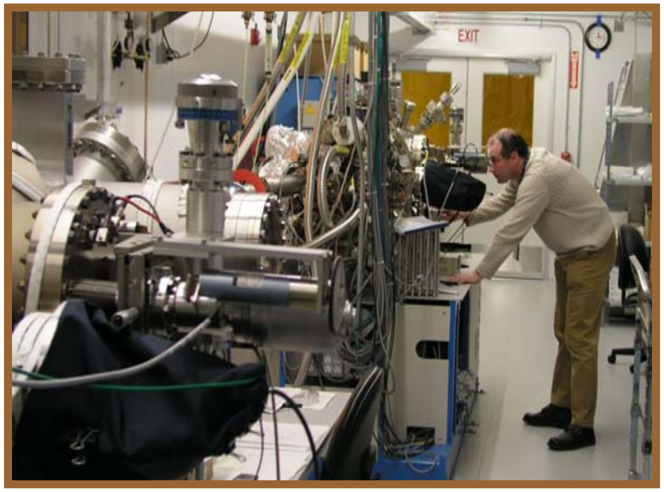
Absorption Depth of Photons in HgCdTe



__Rule of Thumb__

Thickness of HgCdTe layer needs to be about equal to the cutoff wavelength

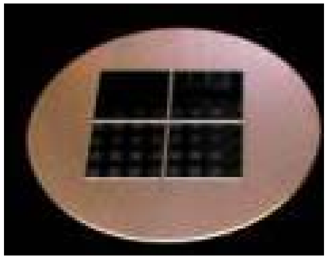
Molecular Beam Epitaxy (MBE) Growth of HgCdTe



RIBER 3-in MBE Systems

3 inch diameter platen allows growth on one 6x6 cm substrate

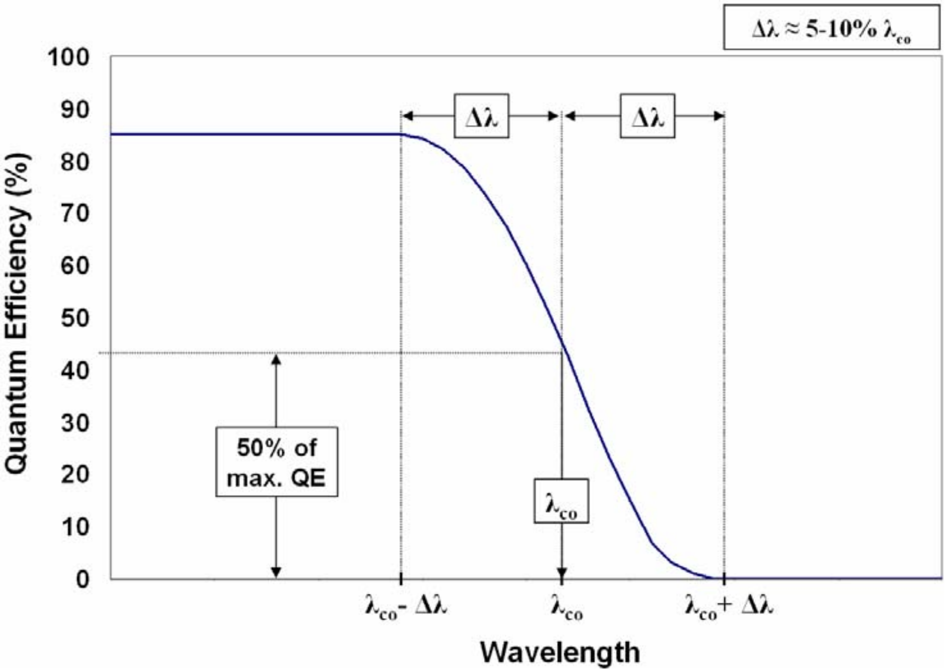
RIBER 10-in MBE 49 System



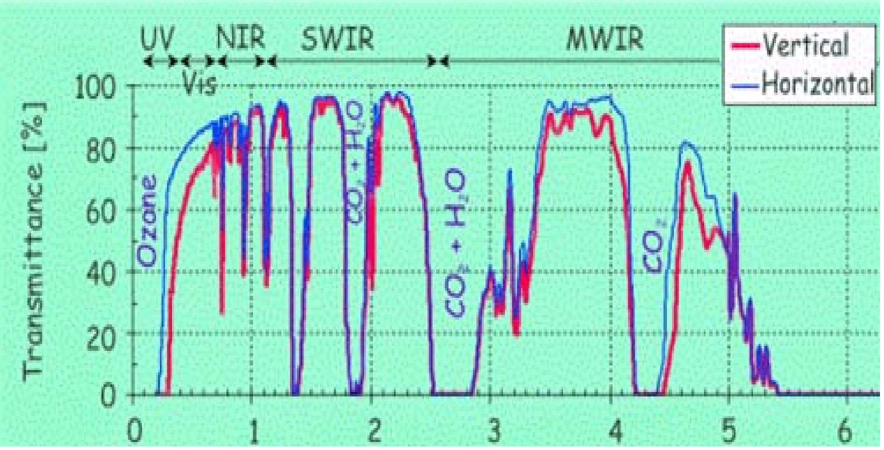
10 inch diameter platen allows simultaneous growth on four 6x6 cm substrates

More than 7500 HgCdTe wafers grown to date

HgCdTe Cutoff Wavelength



Atmospheric Transmission

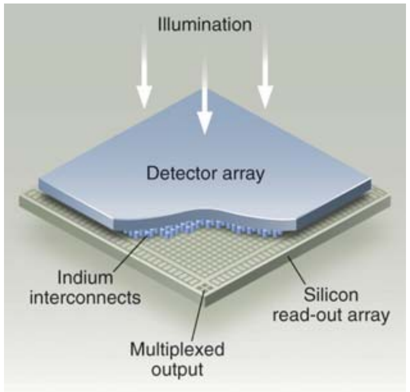


Wavelength (microns)

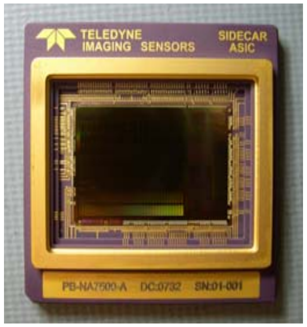
“Standard” Ground-based astronomy cutoff wavelengths

Near infrared (NIR)	**1.75 µm**	**J,H**
Short-wave infrared (SWIR)	**2.5 µm**	**J,H,K**
Mid-wave infrared (MWIR)	**5.3 µm**	**J,H,K,L,M**

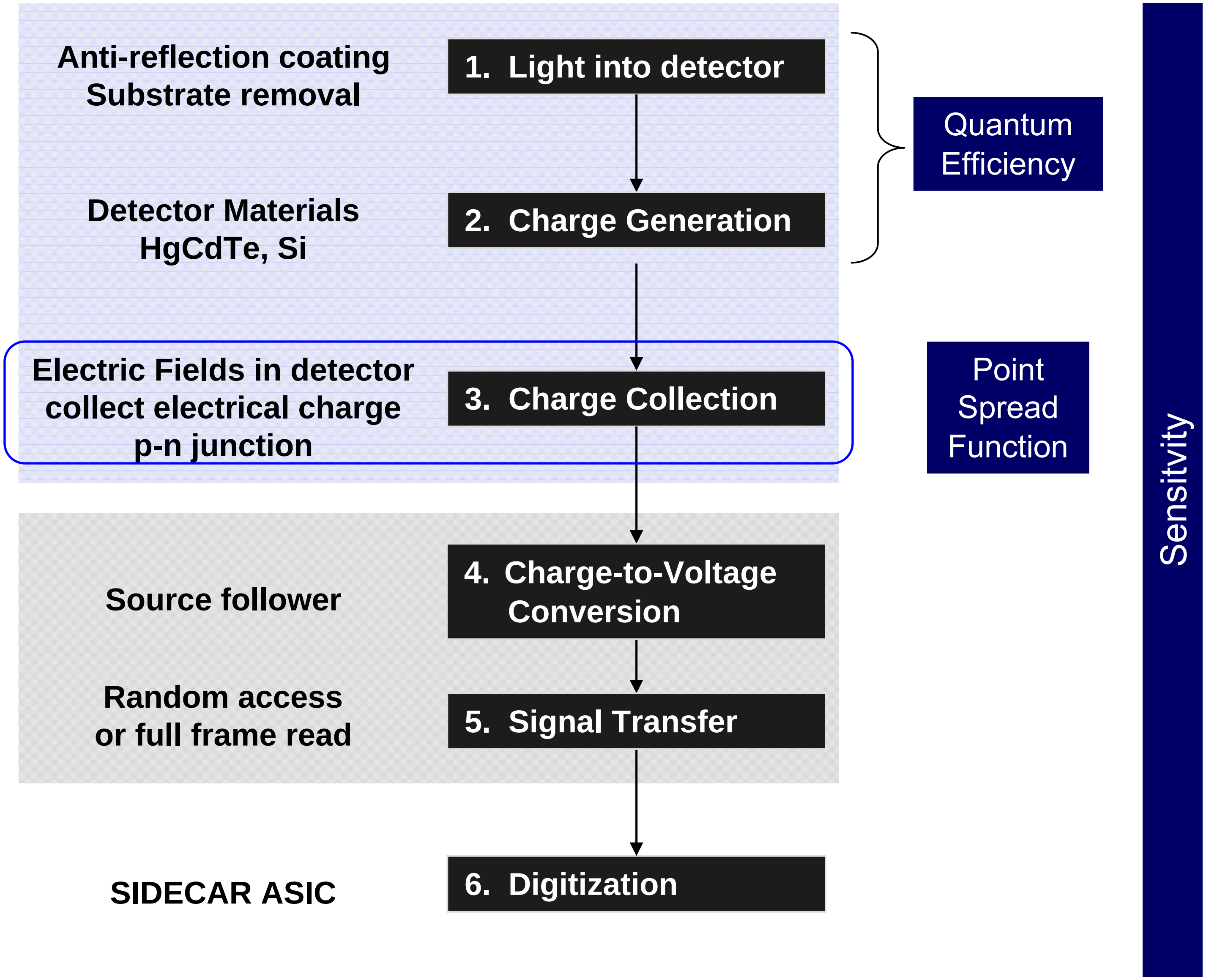
6 Steps of CMOS-based Optical / IR Photon Detection



**HYBRID SENSOR
CHIP ASSEMBLY (SCA)**



SIDECAR ASIC



**Anti-reflection coating
Substrate removal**

1. Light into detector

**Detector Materials
HgCdTe, Si**

2. Charge Generation

Quantum Efficiency

**Electric Fields in detector
collect electrical charge
p-n junction**

3. Charge Collection

Point Spread Function

Source follower

4. Charge-to-Voltage Conversion

**Random access
or full frame read**

5. Signal Transfer

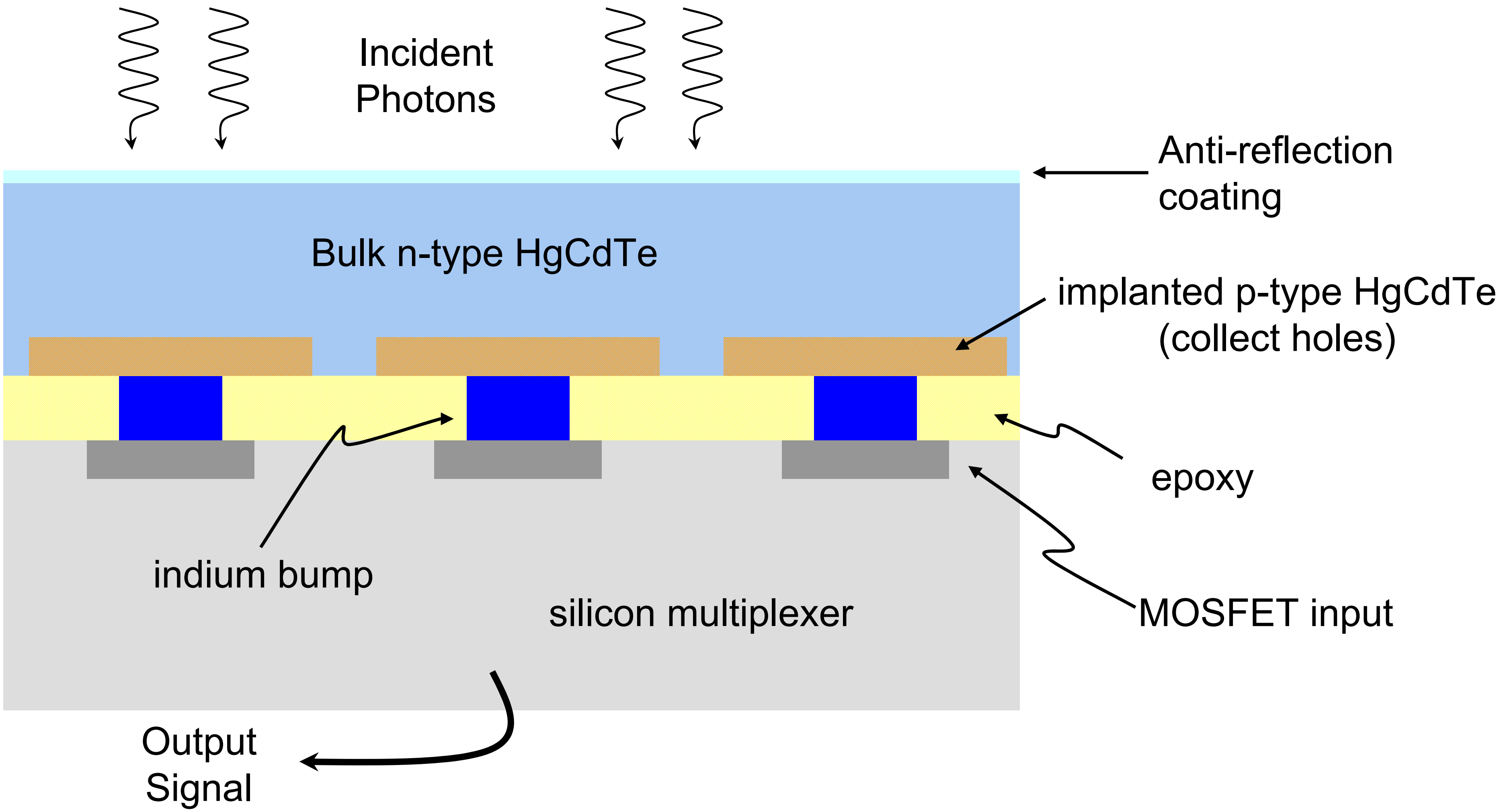
SIDECAR ASIC

6. Digitization

Sensitivity

TELEDYNE
IMAGING SENSORS
A Teledyne Technologies Company

HgCdTe hybrid FPA cross-section (substrate removed)



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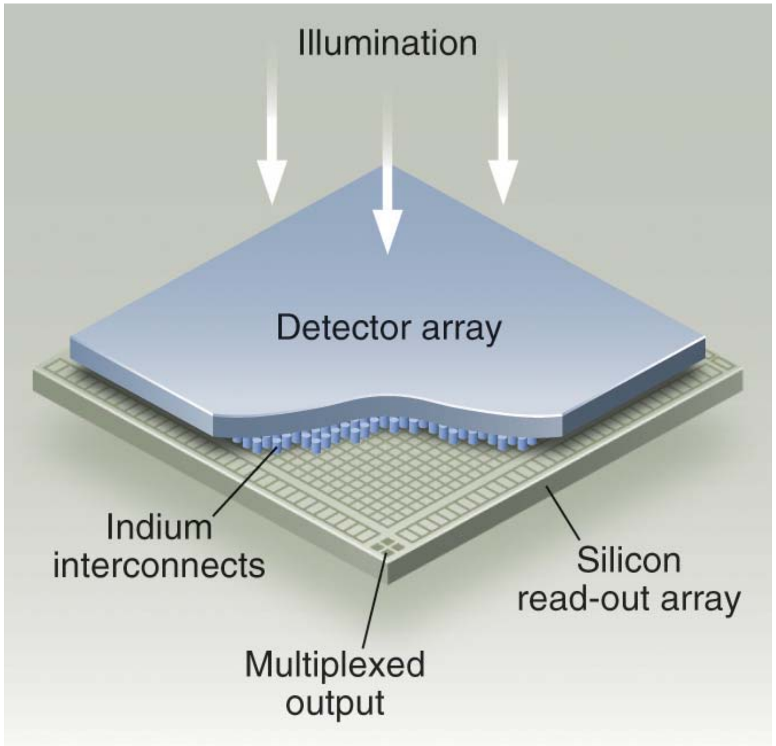
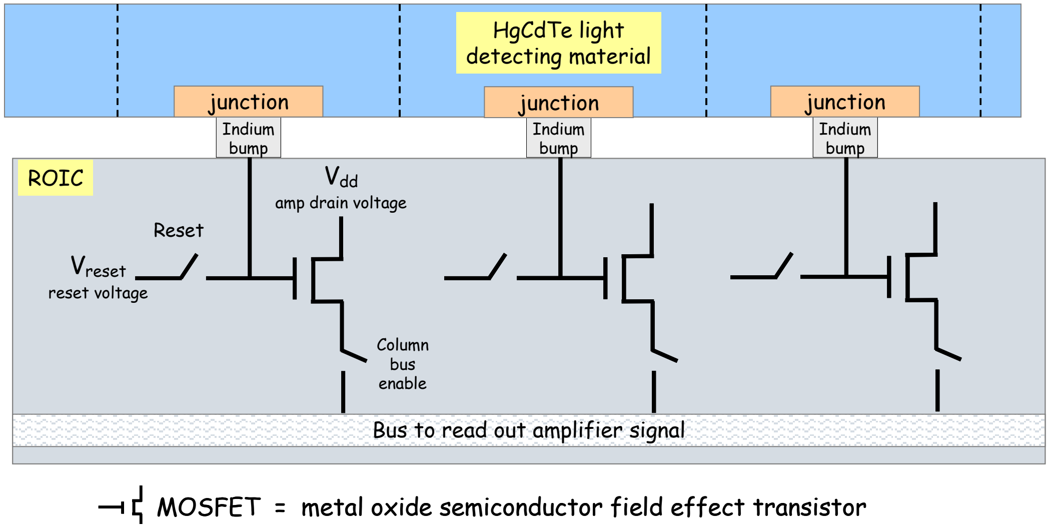
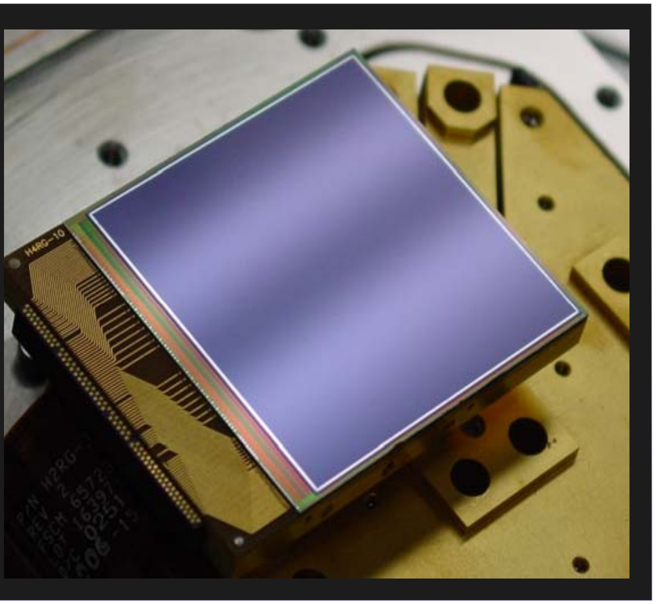
Hybrid Imager Architecture



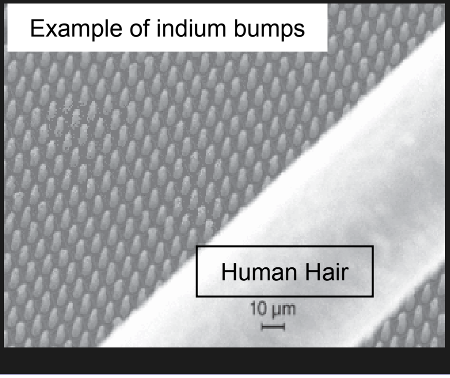


H4RG-10
4096x4096 pixels
10 micron pixel pitch
HyViSI silicon PIN



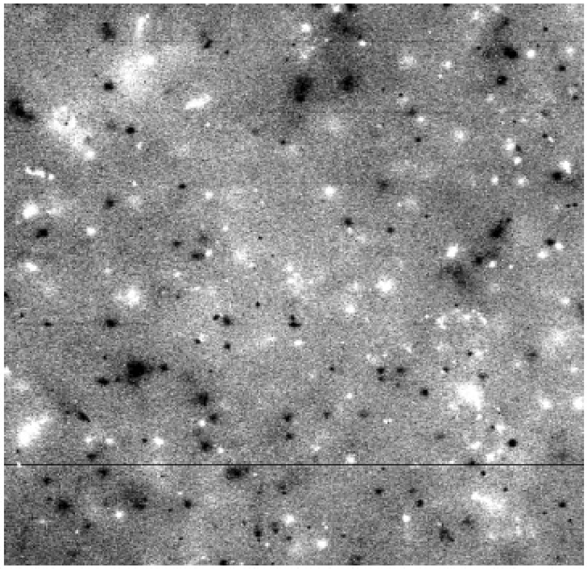
Mature interconnect technique:

- Over 16,000,000 indium bumps per Sensor Chip Assembly (SCA) demonstrated
- >99.9% interconnect yield

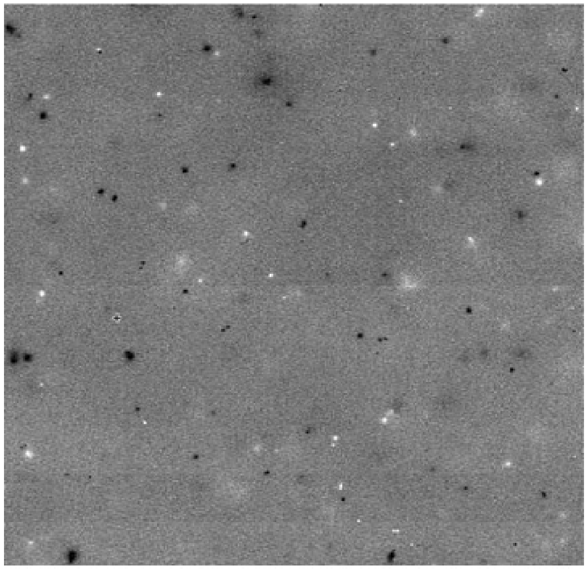


Cosmic Rays and Substrate Removal

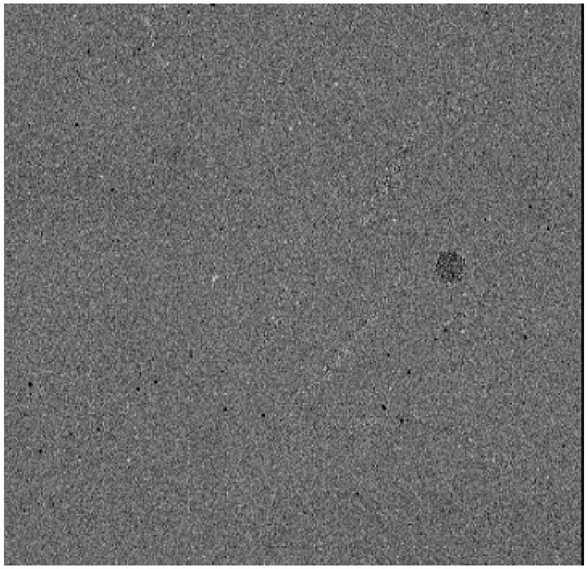
- Cosmic ray events produce clouds of detected signal due to particle-induced flashes of infrared light in the CdZnTe substrate; removal of the substrate eliminates the effect



2.5um cutoff, substrate **on**



1.7um cutoff, substrate **on**



1.7um cutoff, substrate **off**

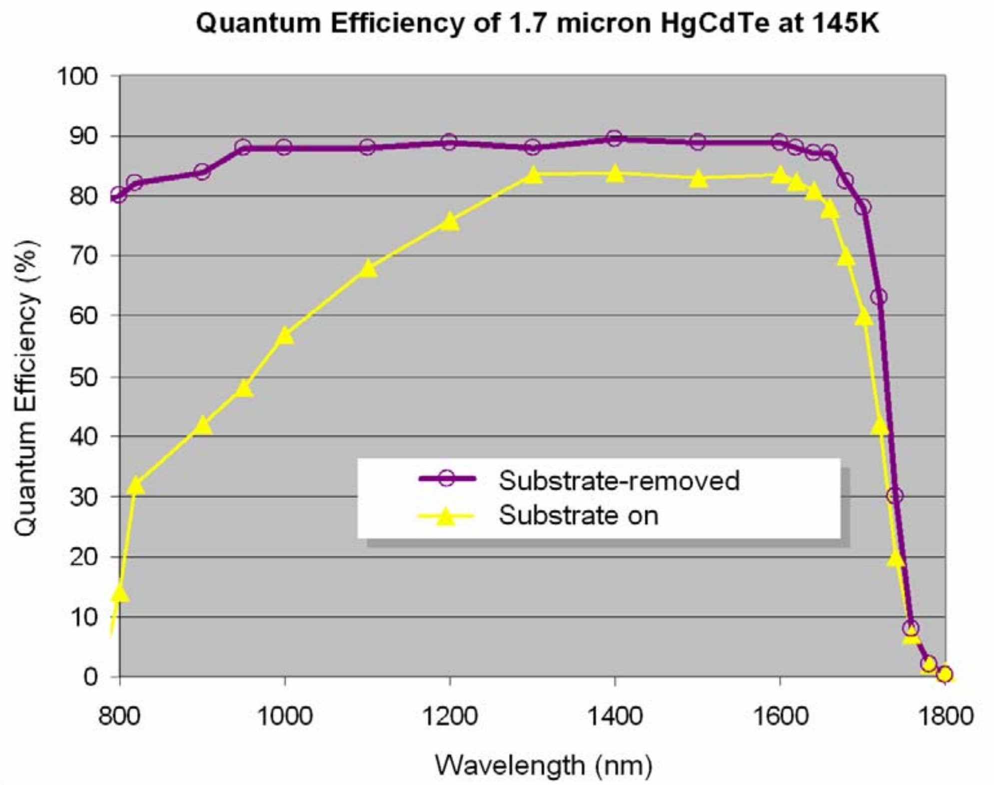
Substrate Removal Positive Attributes

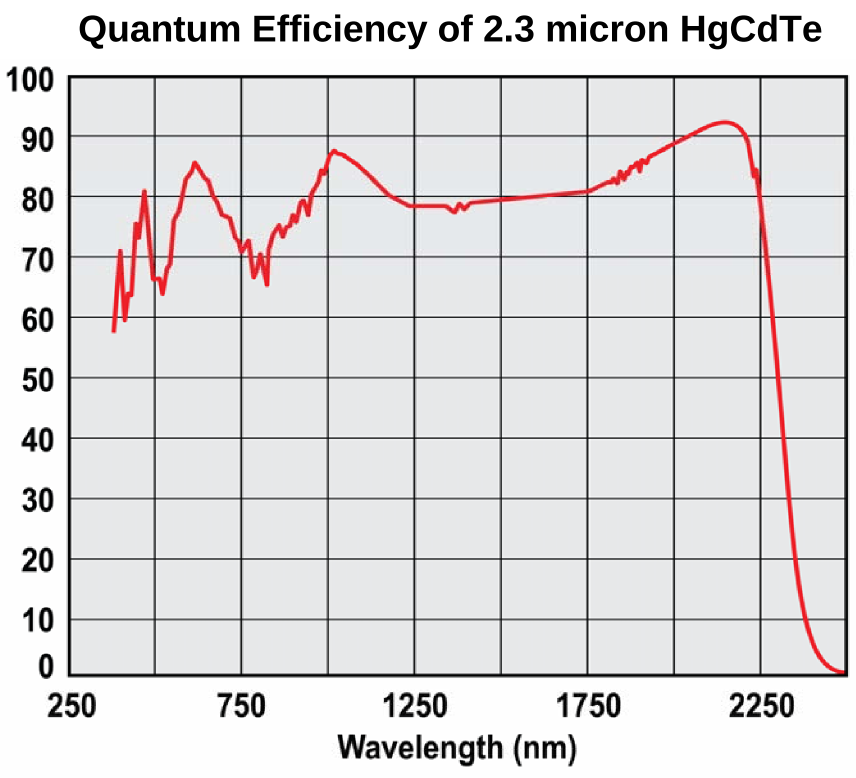
1. **Higher QE in the near infrared**
2. **Visible light response**
3. **Eliminates cosmic ray fluorescence**
4. **Eliminates CTE mismatch with silicon ROIC**

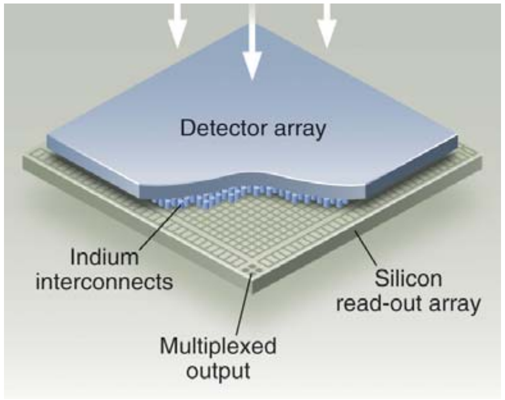
TELEDYNE IMAGING SENSORS
A Teledyne Technologies Company

Images courtesy of Roger Smith

Quantum Efficiency of substrate-removed HgCdTe







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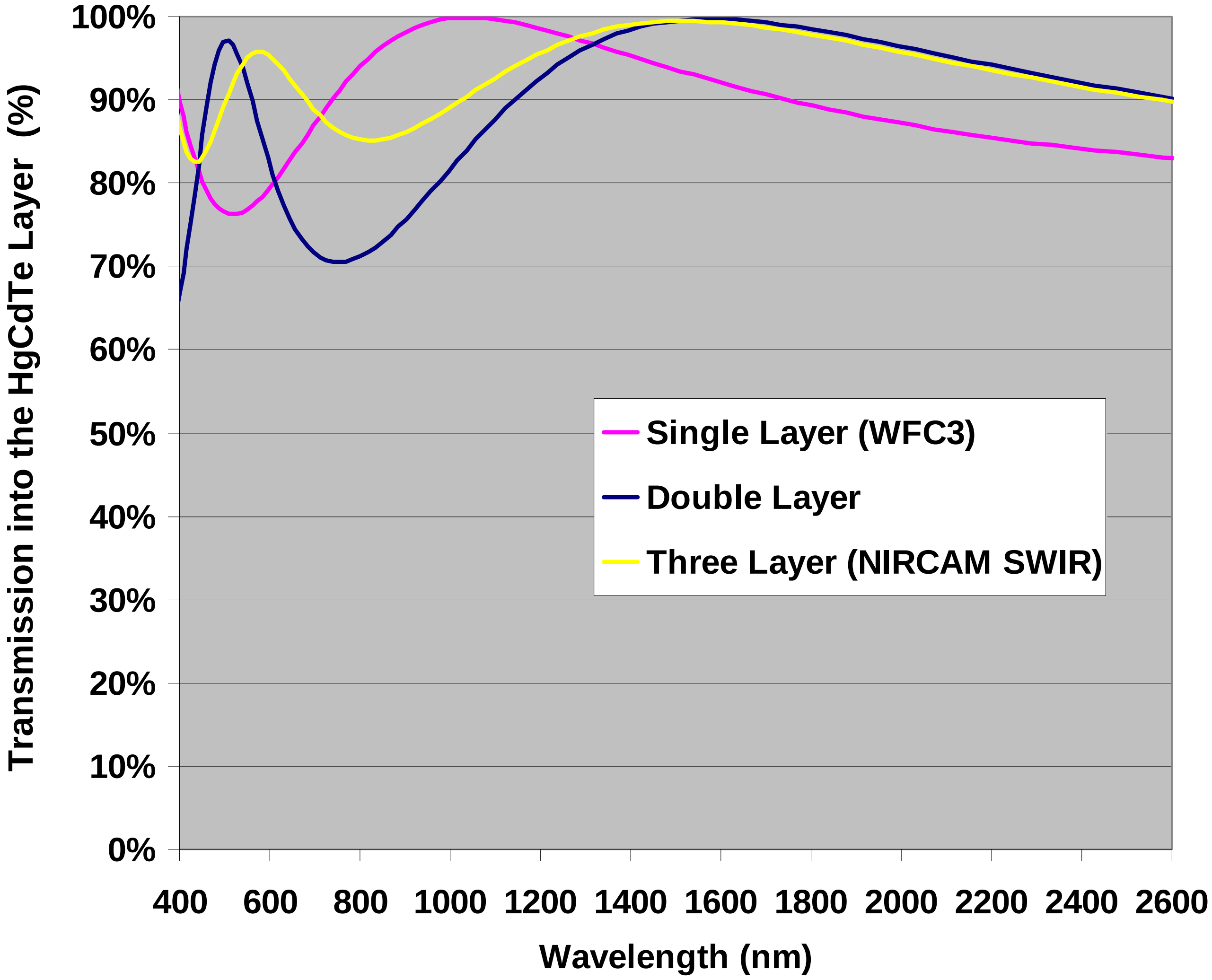
Example Anti-reflection coatings for HgCdTe



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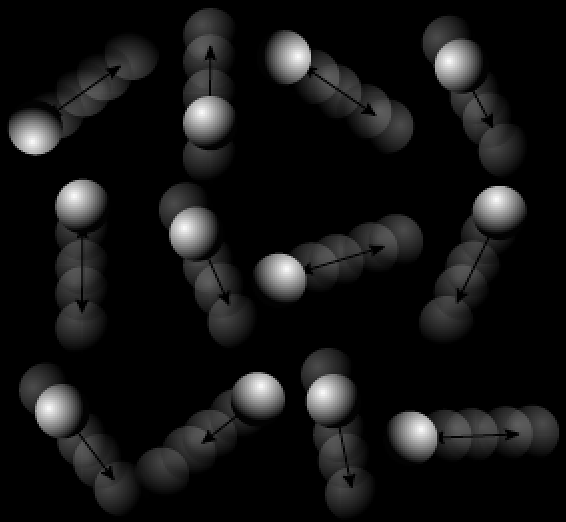
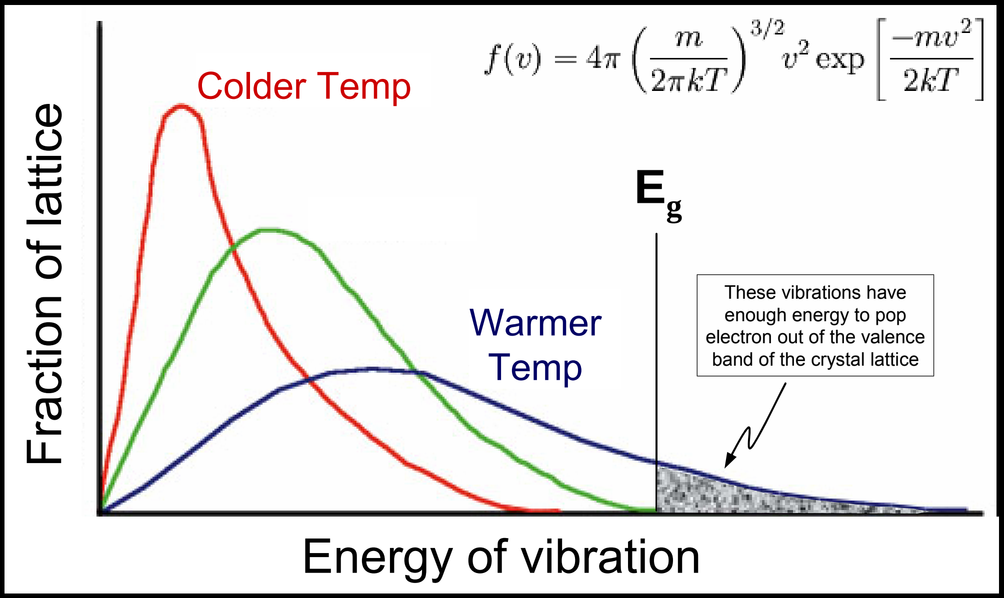
Dark Current

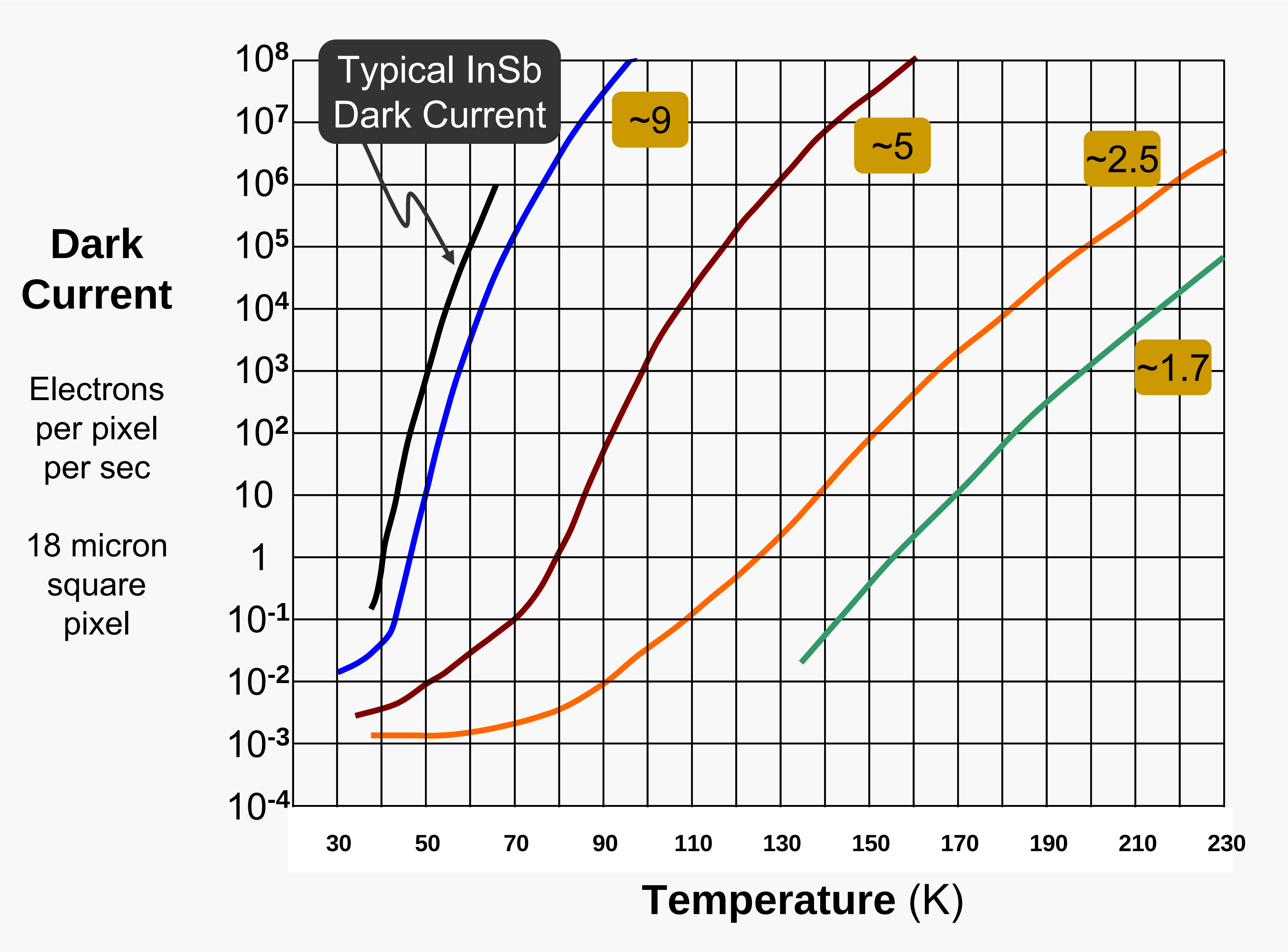
Undesirable byproduct of light detecting materials





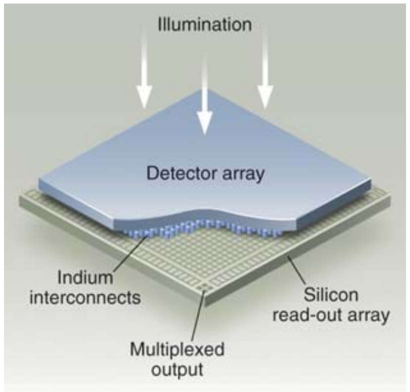
- The vibration of particles (includes crystal lattice phonons, electrons and holes) has energies described by the Maxwell-Boltzmann distribution. Above absolute zero, some vibration energies may be larger than the bandgap energy, and will cause electron transitions from valence to conduction band.
- Need to cool detectors to limit the flow of electrons due to temperature, i.e. the **dark current** that exists in the absence of light.
- The smaller the bandgap, the colder the required temperature to limit dark current below other noise sources (e.g. readout noise)

Dark Current of MBE HgCdTe

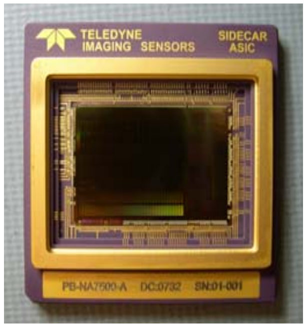


HgCdTe cutoff wavelength (microns)

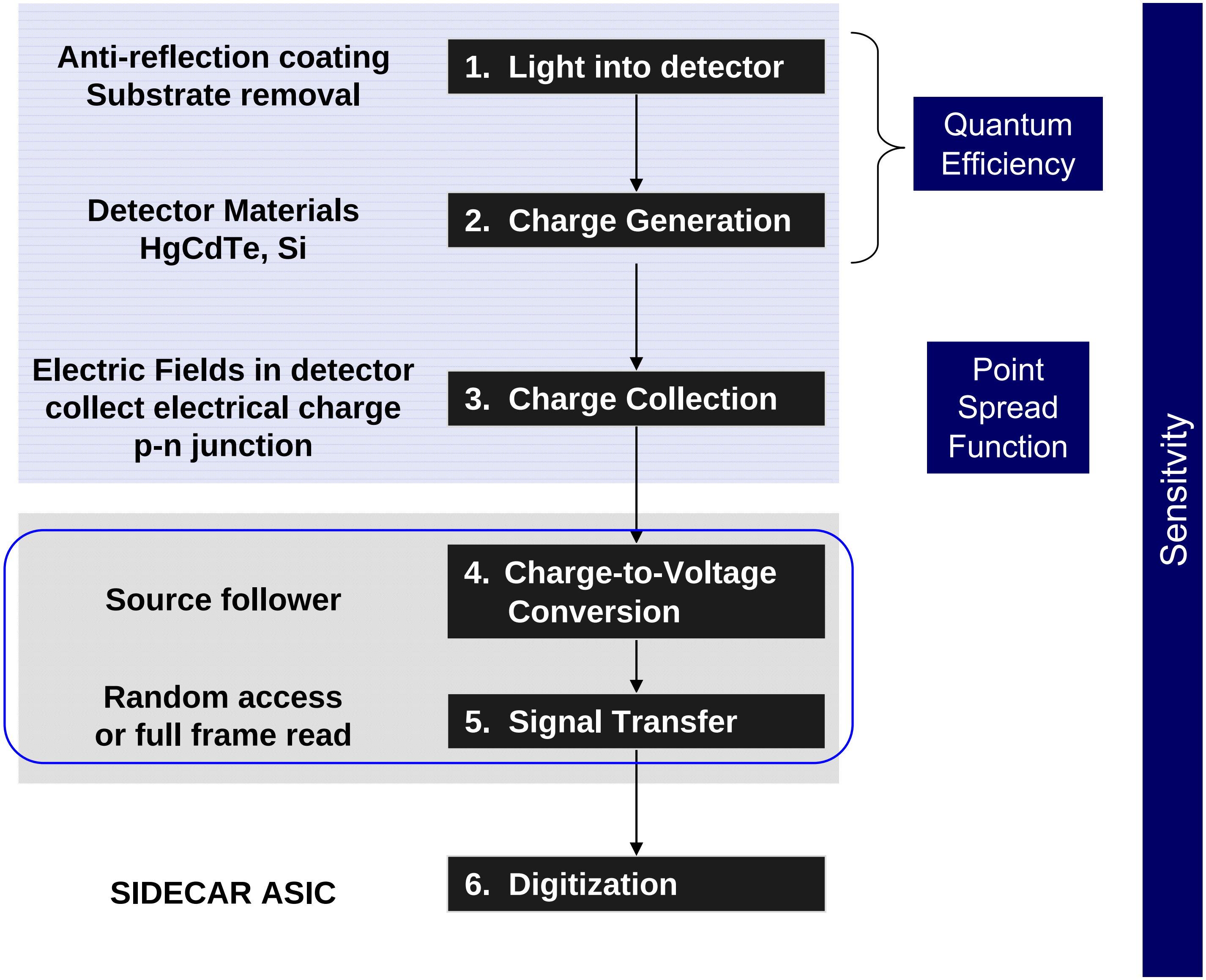
6 Steps of CMOS-based Optical / IR Photon Detection



HYBRID SENSOR CHIP ASSEMBLY (SCA)



SIDECAR ASIC



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Electric Fields in detector
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p-n junction

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Point Spread Function

Source follower

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Random access
or full frame read

5. Signal Transfer

SIDECAR ASIC

6. Digitization

Sensitivity

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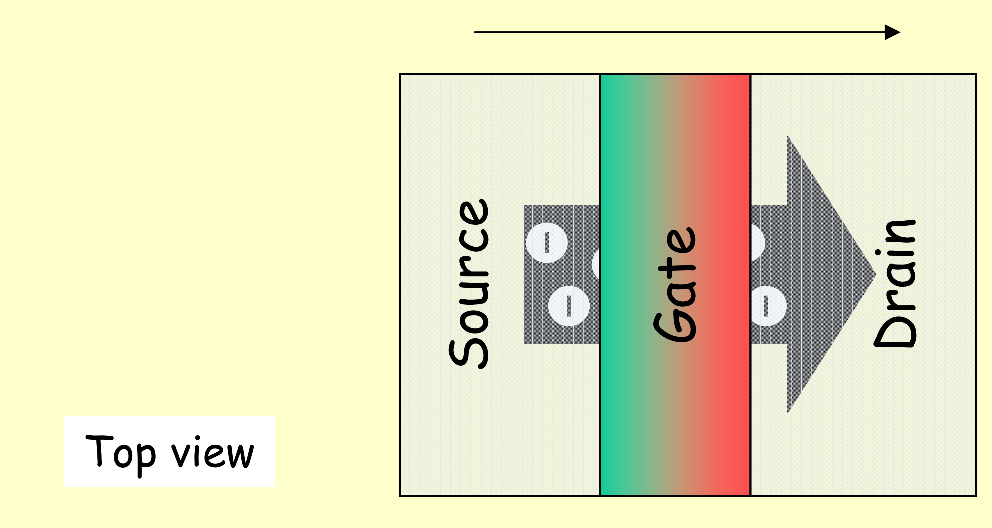
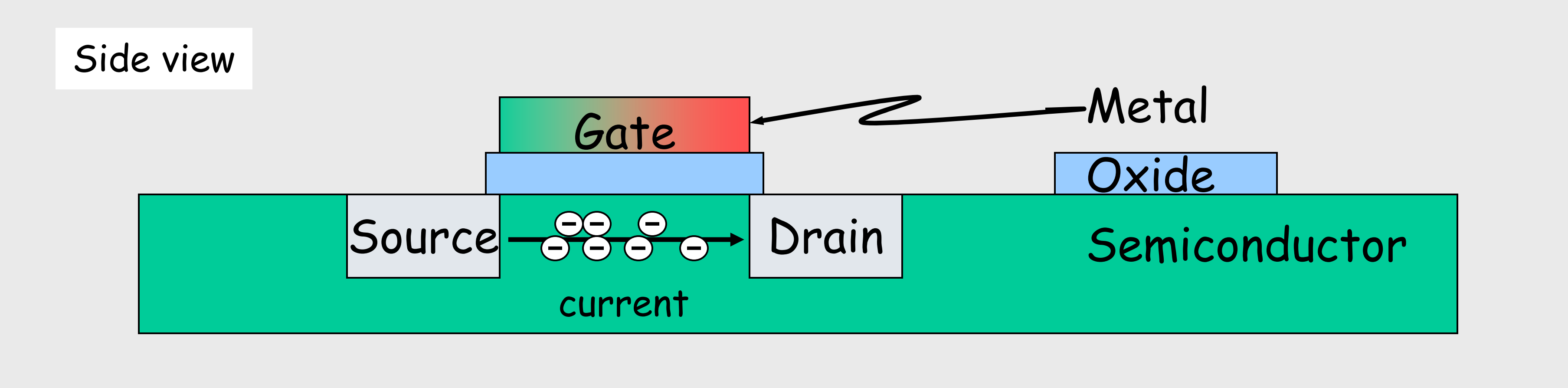
MOSFET Principles

MOSFET = metal oxide semiconductor field effect transistor



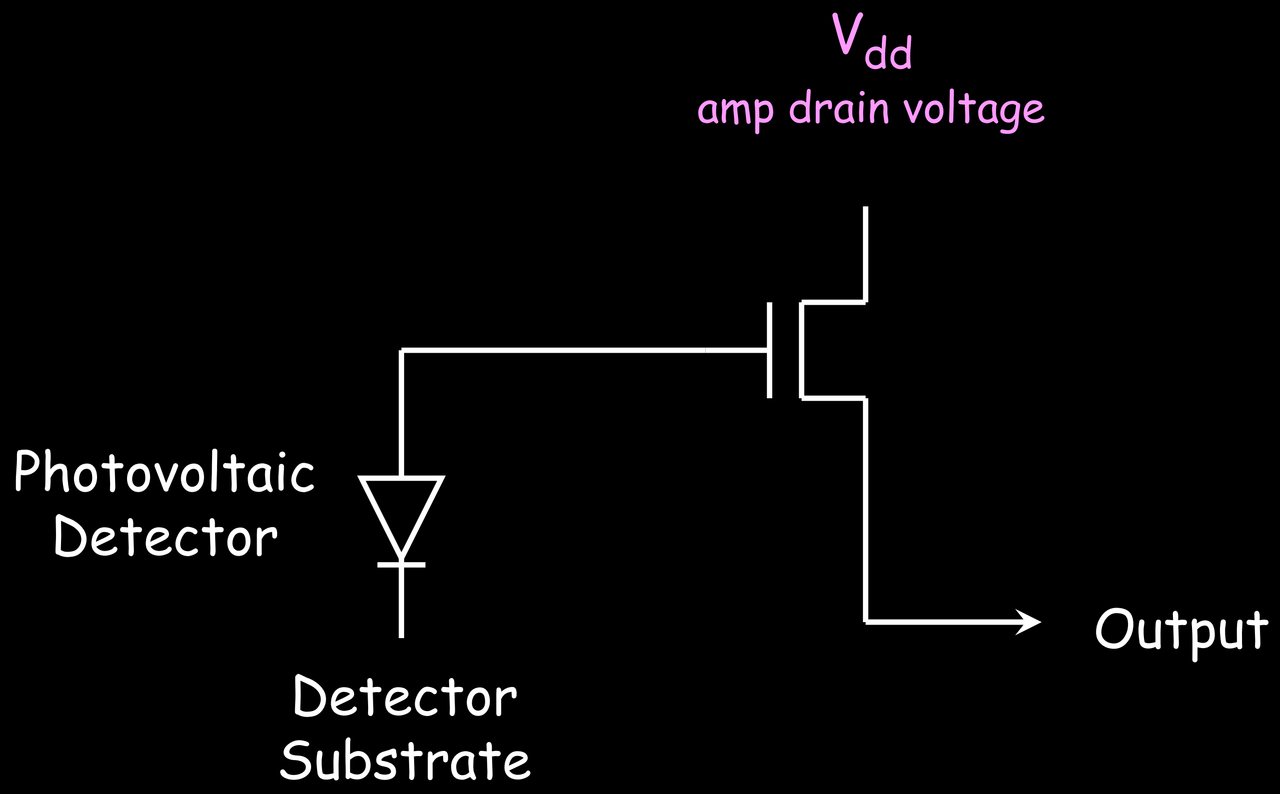
Turn on the MOSFET and current flows from source to drain

Add charge to gate & the current flow changes since the effect of the field of the charge will reduce the current

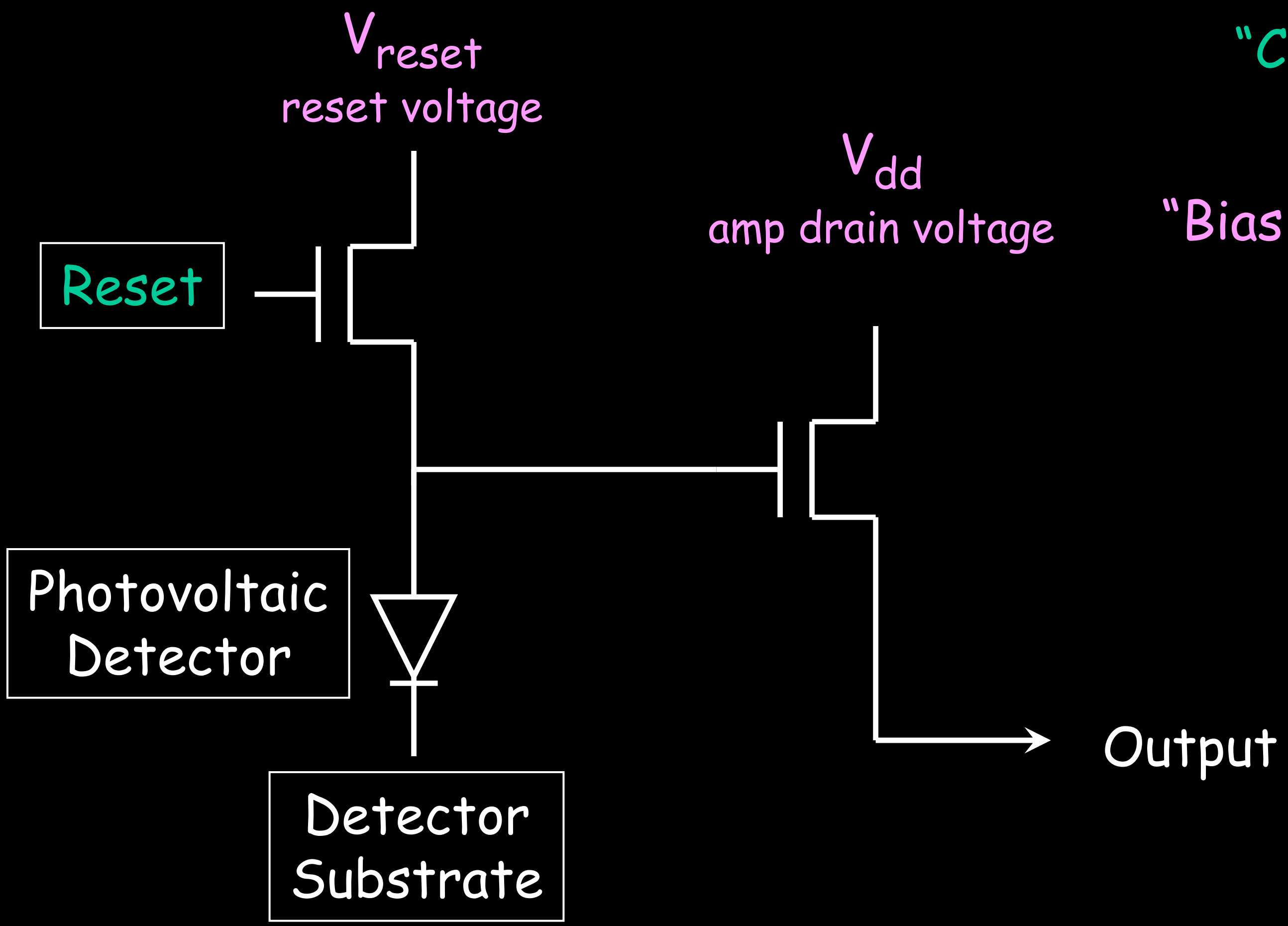


Fluctuations in current flow produce “readout noise”
Fluctuations in reset level on gate produces “reset noise”

IR multiplexer pixel architecture



IR multiplexer pixel architecture



V_{reset}
reset voltage

V_{dd}
amp drain voltage

Reset

Photovoltaic Detector

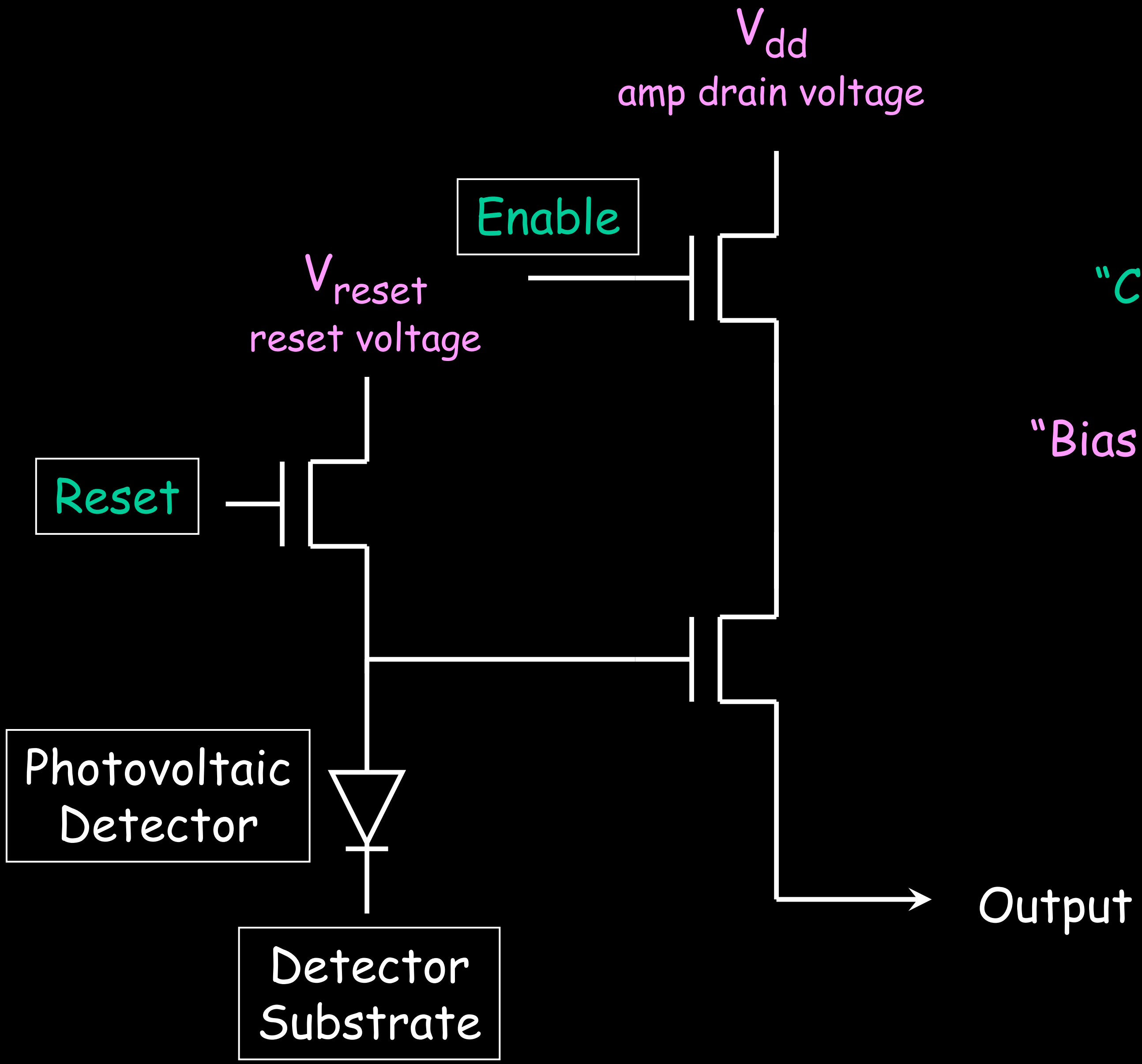
Detector Substrate

Output

“Clock” (green)

“Bias voltage” (purple)

IR multiplexer pixel architecture

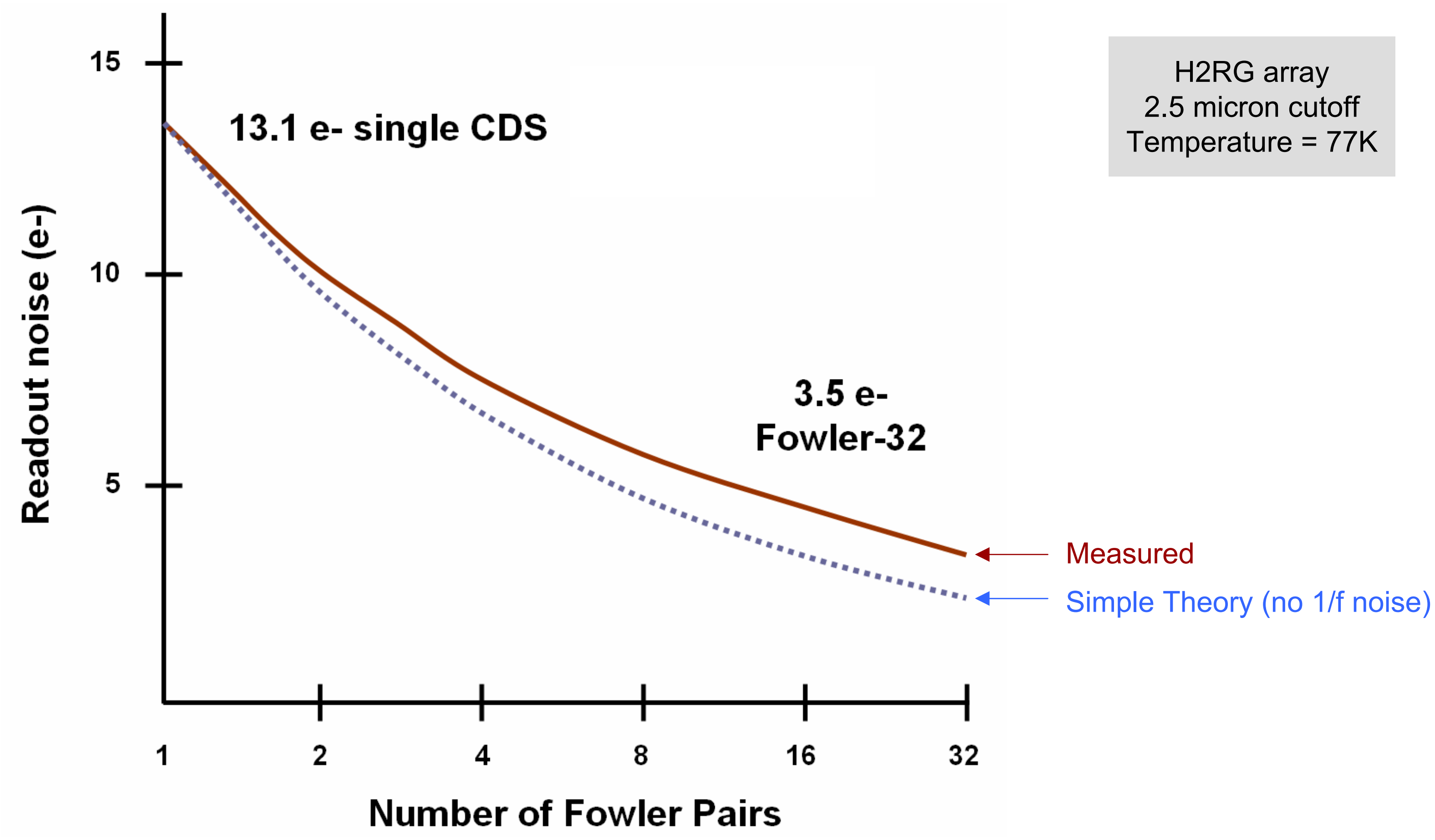


"Clock" (green)

"Bias voltage" (purple)

Reduction of noise from multiple samples

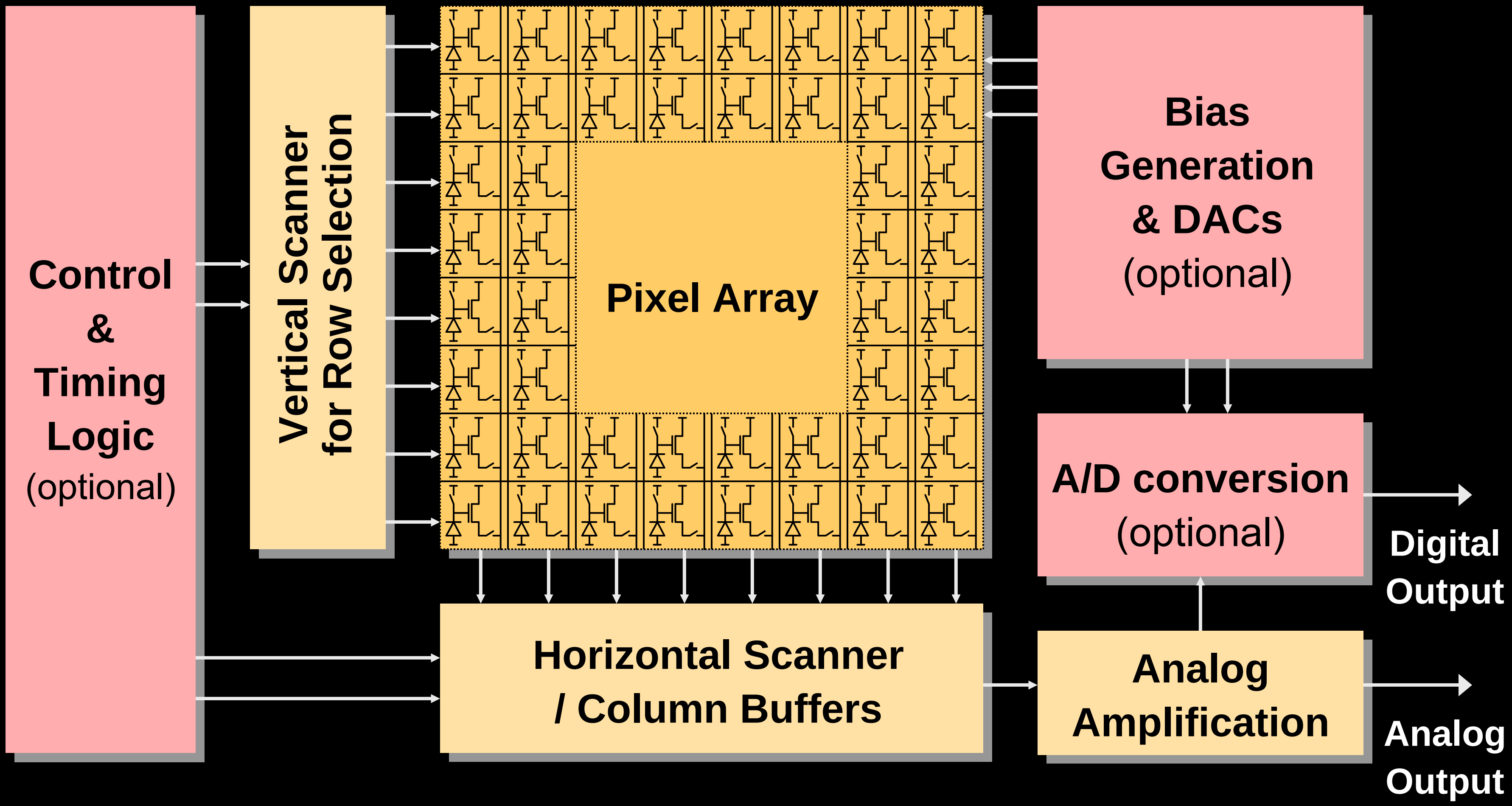
Non-destructive readout enables reduction of noise from multiple samples



H2RG array
2.5 micron cutoff
Temperature = 77K

CDS = correlated double sample

General Architecture of CMOS-Based Image Sensors



Control & Timing Logic (optional)

Vertical Scanner for Row Selection

Pixel Array

Bias Generation & DACs (optional)

A/D conversion (optional)

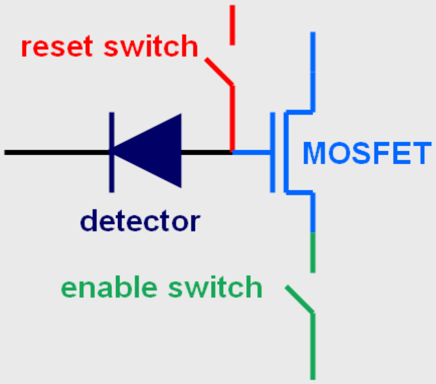
Digital Output

Horizontal Scanner / Column Buffers

Analog Amplification

Analog Output

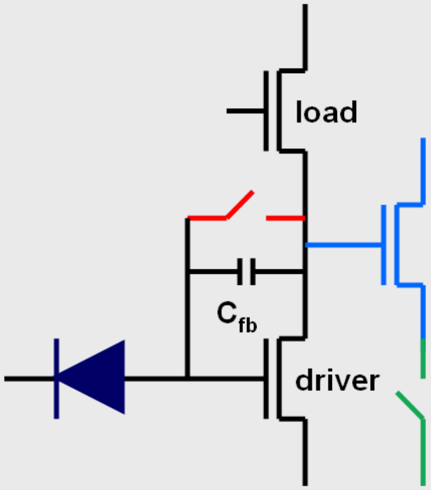
Pixel Amplifier Options



Source follower (SF)

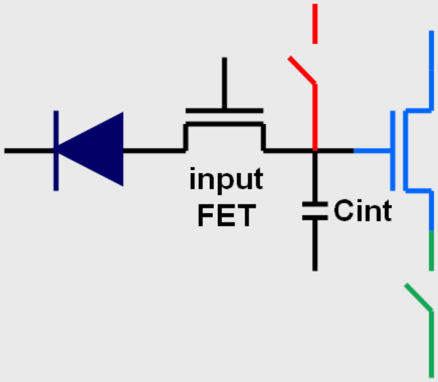
- Integration on detector node
- Low power & compact (3 FETs / pixel)
- Ideal for small pixels & low flux
- Poor performance for high flux

- Full Well: ~100,000 electrons
- Readout Noise: <15 e-



Capactive TransImpedance Amplifier (CTIA)

- Versatile circuit suitable for all backgrounds and detectors
- High linearity
- High power, higher noise and larger circuit than SF for low flux
- Worse performance than DI for high flux
- Full Well: ~1 to 10 million e-
- Readout Noise: <50 e-

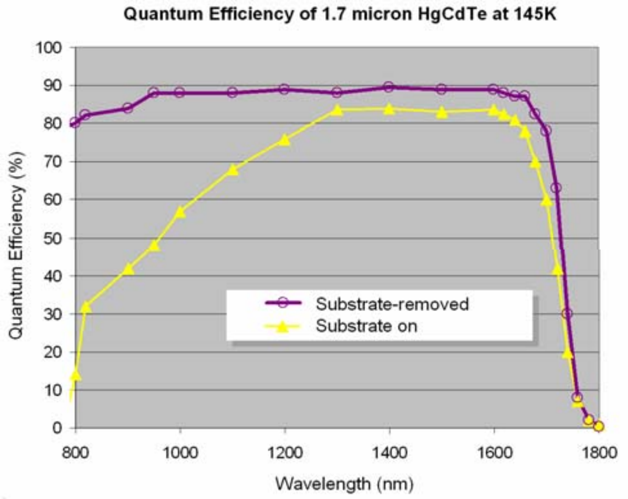


Direct Injection (DI)

- Extremely small circuit
- Large integration density in pixel
- High well capacity for high flux applications
- Ultra low power
- Poor injection efficiency for low flux applications
- Full Well: tens of millions of e-
- Readout Noise: <1000 e-

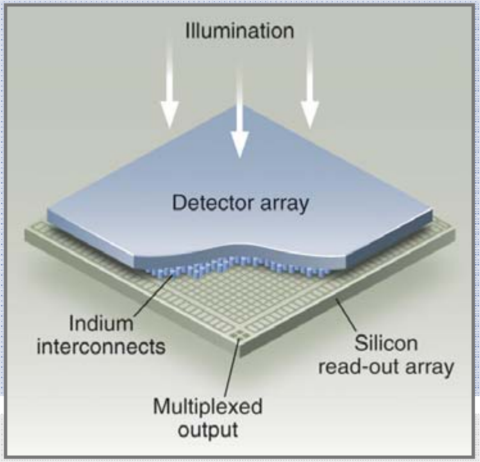
High Performance Hybrid CMOS Arrays

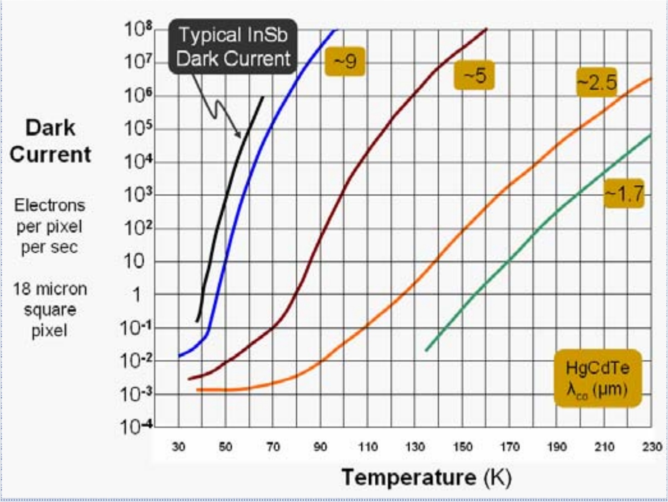
High Quality MBE HgCdTe + High Performance CMOS Design + Large Area Hybridization



High Quantum Efficiency

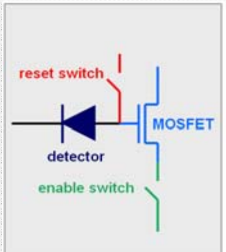
High Quality Detectors





Low Dark Current

High Performance Amplifiers



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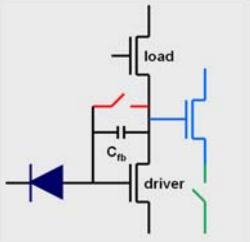

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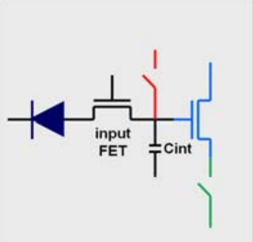

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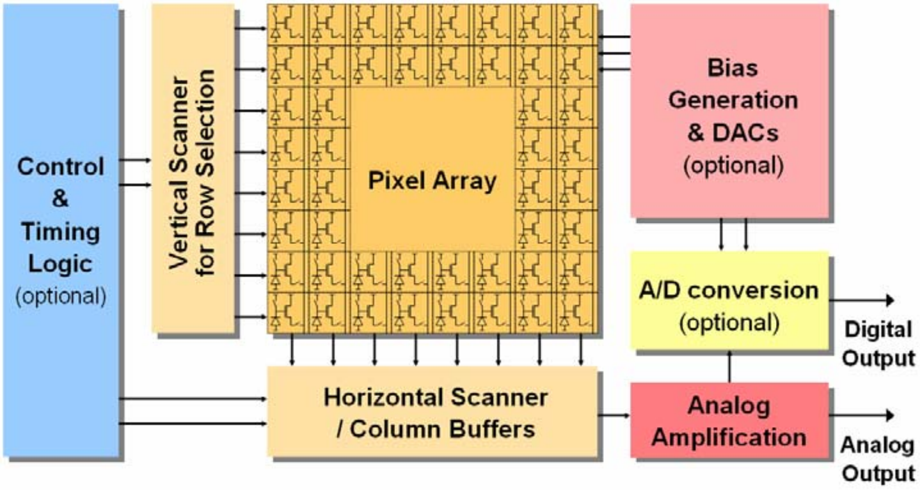
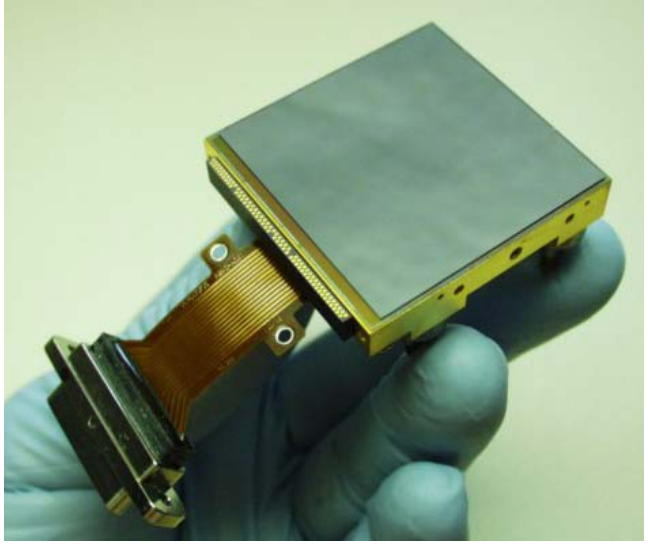
Imaging System on Chip Architecture



High Performance Readout Circuits

HAWAII-2RG 2048×2048 pixels



4Kx4K mosaic of 4 H2RGs

HAWAII-2RG (H2RG)

- 2048×2048 pixels, 18 micron pitch
- 1, 2, 4, 32 ports
- “R” = reference pixels (4 rows/cols at edge)
- “G” = guide window
- Low power: <1 mW (4 port, 100 kHz rate)
- Detector material: HgCdTe or Si
- Interfaces directly to the SIDECAR ASIC

- **Qualified to NASA TRL-6**
  - Vibration, radiation, thermal cycling
  - Radiation hard to ~100 krad

Teledyne Imaging Sensors
HAWAII-2RG™
Visible & Infrared Focal Plane Array

The 2048×2048 pixel HAWAII-2RG™ (H2RG) is the state-of-the-art readout integrated circuit for visible and infrared astronomy in ground-based and space telescope applications.

- Large (2048×2048 pixel) array with 18 µm pixel pitch.
- Compatible with Teledyne Imaging Sensors (TIS) HgCdTe infrared (IR) and silicon PIN HyViSI™ visible detectors, providing sensing of any spectral band from soft X-ray to 5.5 µm.
- Substrate-removed HgCdTe enhances the J-band QE, enables response into the visible spectrum (70% QE down to 400nm) and eliminates fluorescence from cosmic radiation absorbed in the substrate.
- Reference rows and columns for common-mode noise rejection.
- Guide window output – windowing with simultaneous science date acquisition of full array. Programmable window which may be read out at up to 5 MHz pixel rate for guiding. Readout is designed to allow interleaved readout of the guide window and the full frame science data.
- Selectable number of outputs (1, 4, or 32) and user-selectable scan directions provide complete flexibility in data acquisition.
- Built with modularity in mind – the array is 4-side-buttable to allow assembly of large mosaics of 2048×2048 H2RG modules, such as TIS' 4096×4096 mosaic FPA and larger mosaics.
- Fully compatible with the TIS SIDECAR™ ASIC Focal Plane Electronics.

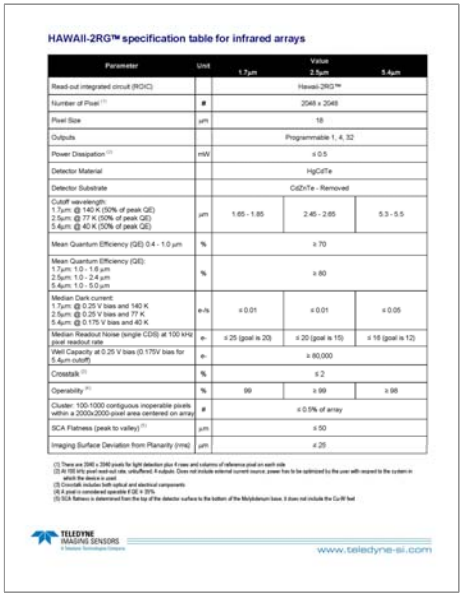
H2RG

2×2 mosaic of H2RGs

5×7 mosaic of H2RGs (engineering model)

*For more information, please email **Richard Blank** at **rblank@teledyne.com** or call +1 **805 373-4083.***

www.teledyne-si.com



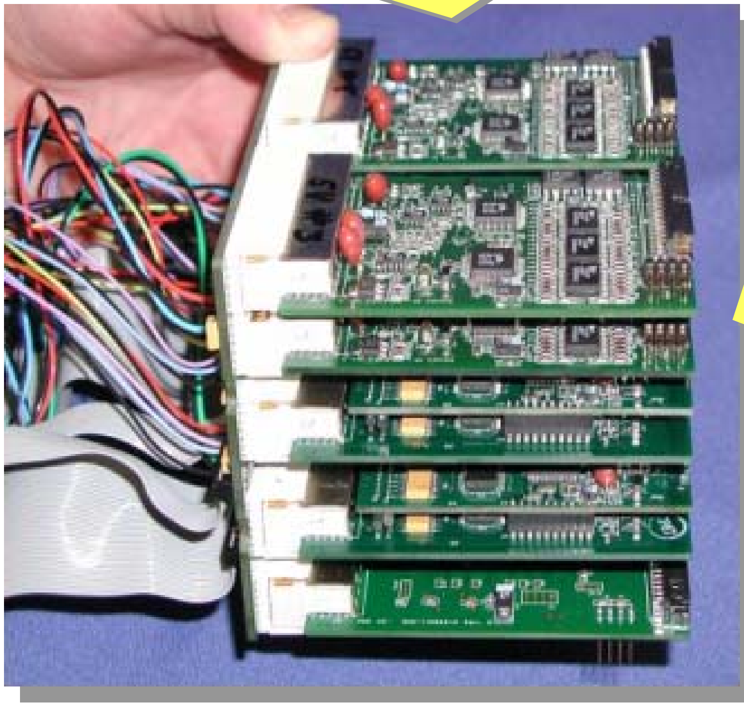
HAWAII-2RG™ specification table for infrared arrays

Parameter	Unit	Value 1.7µm	 2.5µm	 5.4µm
Read-out integrated circuit (ROIC)		Hawaii-2RG™		
Number of Pixel (1)	#	2048 x 2048		
Pixel Size	µm	18		
Outputs		Programmable 1, 4, 32		
Power Dissipation (2)	mW	≤ 0.5		
Detector Material		HgCdTe		
Detector Substrate		CdZnTe - Removed		
Cutoff wavelength: 1.7µm: @ 140 K (50% of peak QE) 2.5µm: @ 77 K (50% of peak QE) 5.4µm: @ 40 K (50% of peak QE)	µm	1.65 - 1.85	2.45 - 2.65	5.3 - 5.5
Mean Quantum Efficiency (QE) 0.4 - 1.0 µm	%	≥ 70		
Mean Quantum Efficiency (QE): 1.7µm: 1.0 - 1.6 µm 2.5µm: 1.0 - 2.4 µm 5.4µm: 1.0 - 5.0 µm	%	≥ 80		
Median Dark current: 1.7µm: @ 0.25 V bias and 140 K 2.5µm: @ 0.25 V bias and 77 K 5.4µm: @ 0.175 V bias and 40 K	e-/s	≤ 0.01	≤ 0.01	≤ 0.05
Median Readout Noise (single CDS) at 100 kHz pixel readout rate	e-	≤ 25 (goal is 20)	≤ 20 (goal is 15)	≤ 18 (goal is 12)
Well Capacity at 0.25 V bias (0.175V bias for 5.4µm cutoff)	e-	≥ 80,000		
Crosstalk (3)	%	≤ 2		
Operability (4)	%	99	≥ 99	≥ 98
Cluster: 100-1000 contiguous inoperable pixels within a 2000x2000-pixel area centered on array	#	≤ 0.5% of array		
SCA Flatness (peak to valley) (5)	µm	≤ 50		
Imaging Surface Deviation from Planarity (rms)	µm	≤ 25		

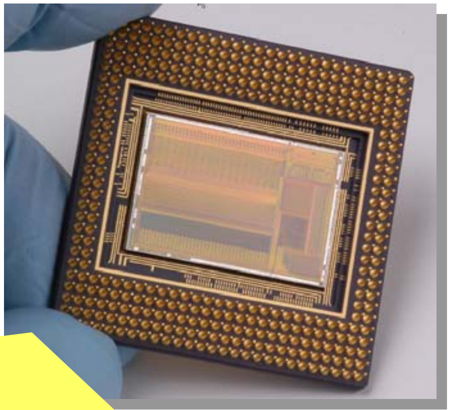
www.teledyne-si.com

The SIDECAR ASIC – Focal Plane Electronics on a Chip

Replace this



with this!



1% volume
1% power
1% hassle

SIDECAR: System for Image Digitization, Enhancement, Control And Retrieval

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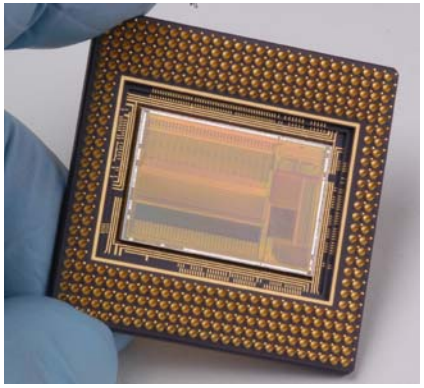
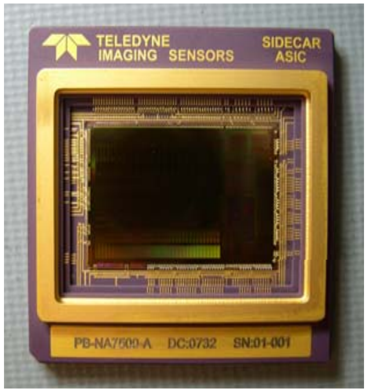
SIDECAR ASIC – Focal Plane Electronics on a Chip

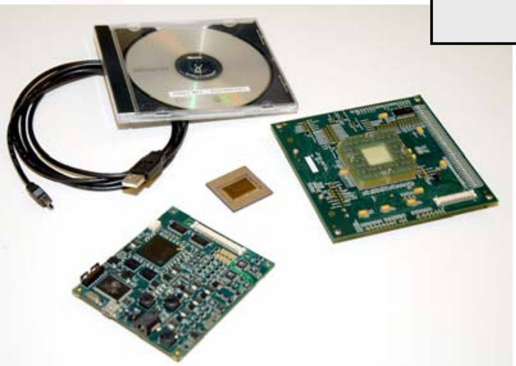


SIDECAR ASIC
Ground-based package



Hubble Space Telescope
SIDECAR ASIC package
(for ACS Repair*)

JWST SIDECAR ASIC package



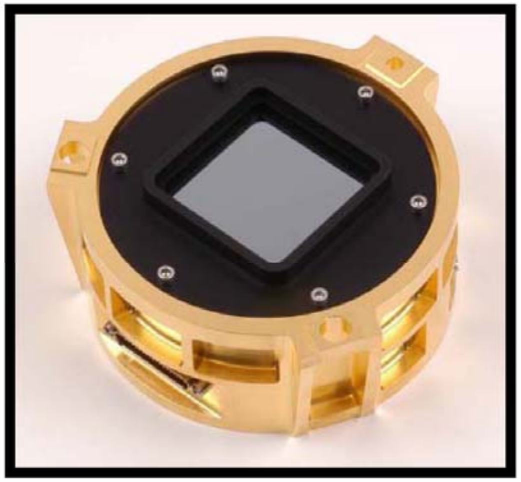
SIDECAR ASIC development kit

SIDECAR ASIC

- 36 analog input channels
- 36 16-bit ADCs: up to 500 kHz
- 36 12-bit ADCs: up to 10 MHz
- 20 output bias channels
- 32 digital I/O channels
- Microcontroller (low power)
- LVDS or CMOS interface
- Low power:
  - <15 mW, 4 channels, 100 kHz, 16-bit ADC
  - <150 mW, 32 channels, 100 kHz, 16-bit ADC
- Operating temperature: 30K to 300K
- Interfaces directly to H1RG, H2RG, H4RG
- **Qualified to NASA TRL-6**
  - Vibration, radiation, thermal cycling
  - Radiation hard to ~100 krad

Spaceflight packaging: JWST Fine Guidance Sensor

FPA - Backside - Cover Removed



Light Facing Side - Scene

PINHOLE EYES | SILICONE OPTICS | OSA 2008 AWARDS

June 2008
Vol. 19 No. 6 | $8.25
www.osa-opn.org

OPN Optics & Photonics News

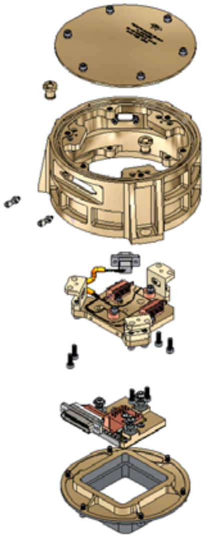
Nonlinear Spatial Solitons

Report from OFC/NFOEC 2008

High Performance
Infrared Focal Plane Arrays

OSA

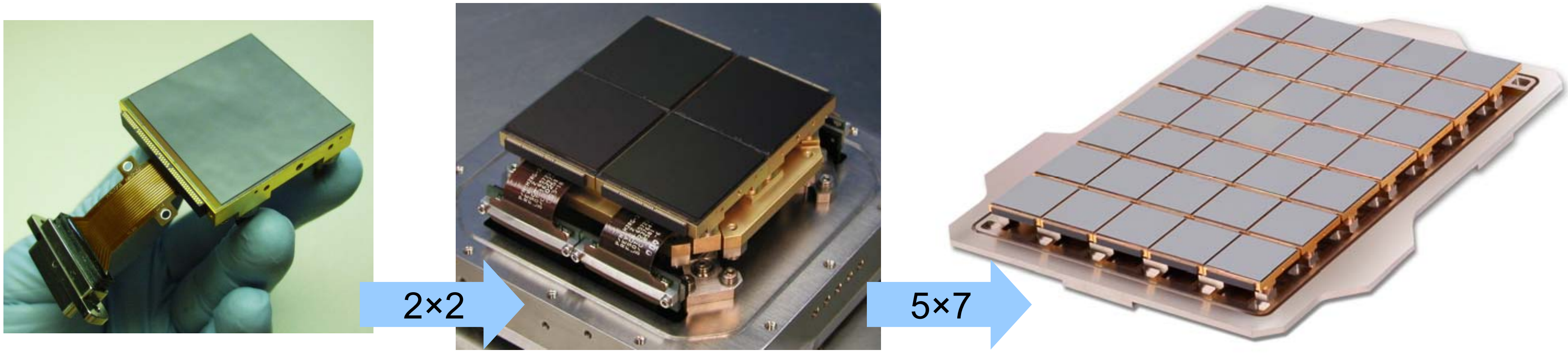
- Package for H2RG 2048x2048 pixel array
- TRL-6 spaceflight qualified
- Interfaces directly to the SIDECAR ASIC
- Robust, versatile package



- **Thermally isolated FPA can be stabilized to 1 mK when cold finger fluctuates several deg K**

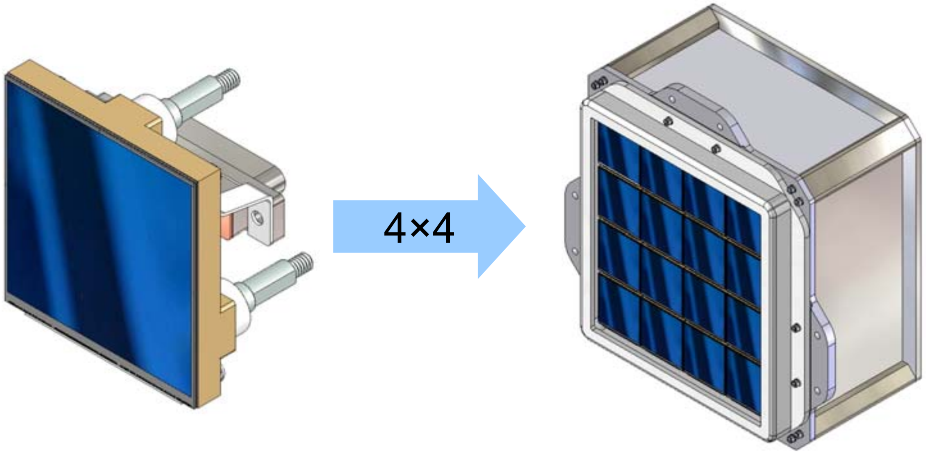
TELEDYNE
IMAGING SENSORS
A Teledyne Technologies Company

SIDECAR ASIC & large mosaic focal plane arrays



H2RG 2K×2K

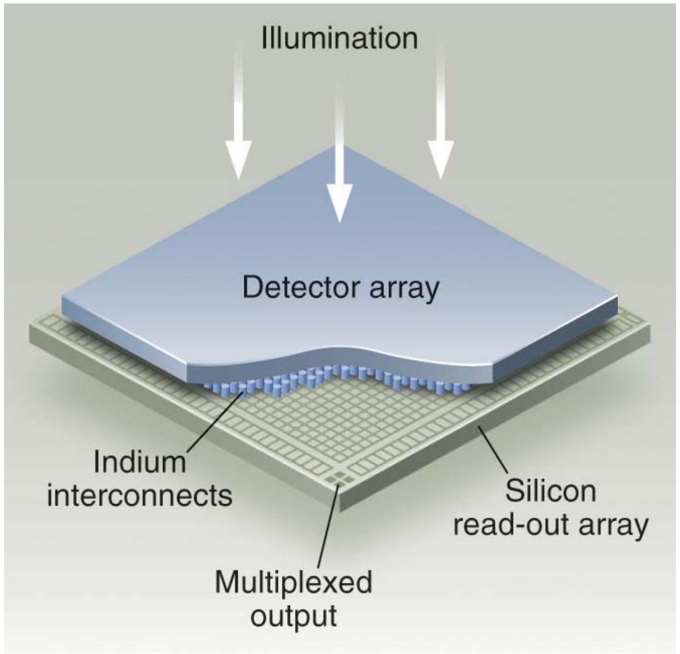
Mechanical Prototype

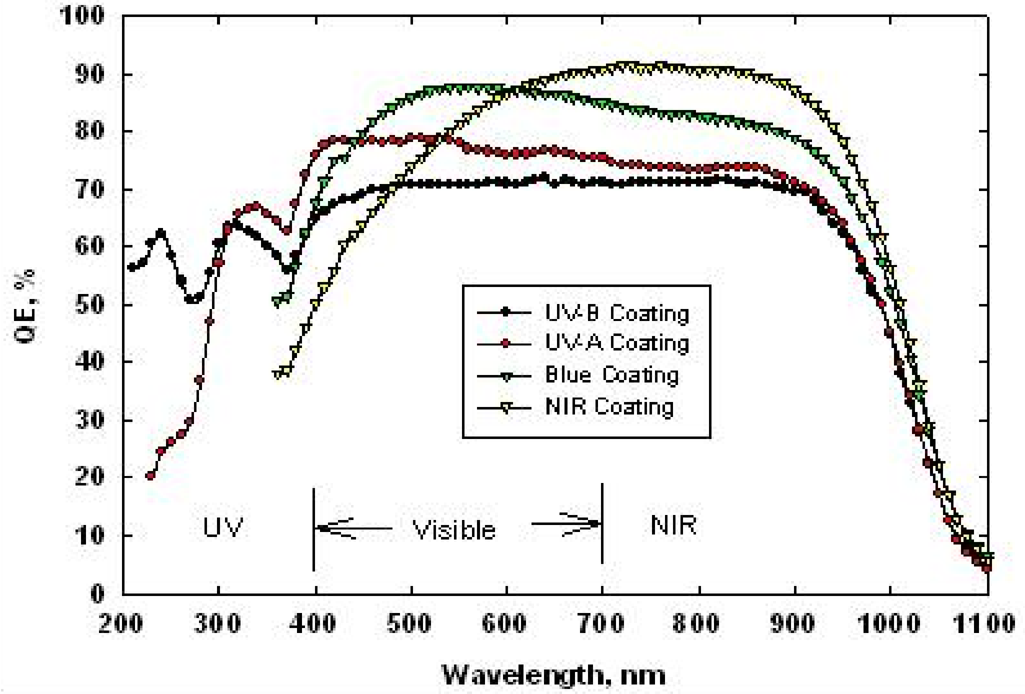


H2RG

4x4 Mosaic
for Space Mission

HyViSI^{TM} – Hybrid Visible Silicon Imager





Focal plane array performance independently verified by:

- Rochester Institute of Technology
- European Southern Observatory
- US Naval Observatory & Goddard Space Flight Center

Readout noise, at 100 kHz pixel rate

- 7 e- single CDS, with reduction by multiple sampling

Pixel operability > 99.99%

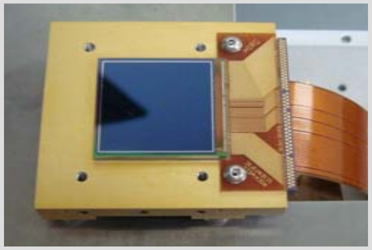
HyViSI Array Formats

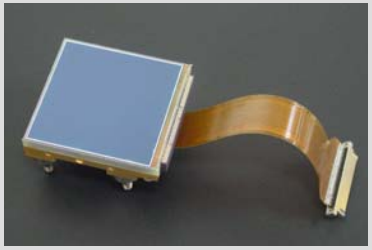
Ground-based Astronomy (Rochester Institute of Technology)

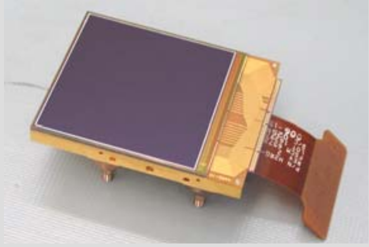

Crab Nebula (M1)

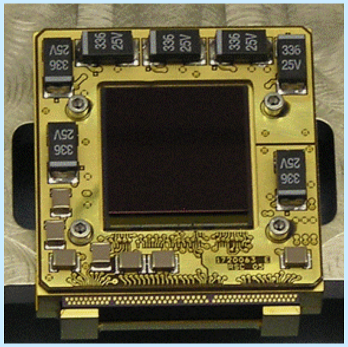

NGC2683 Spiral Galaxy


Hercules Cluster (M13)


1K×1K H1RG-18


2K×2K H2RG-18

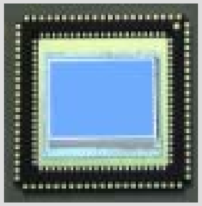

4K×4K H4RG-10



Orbiting Carbon Observatory

1K×1K
H1RG-18
(same used by IR)
Launch: Jan 2009

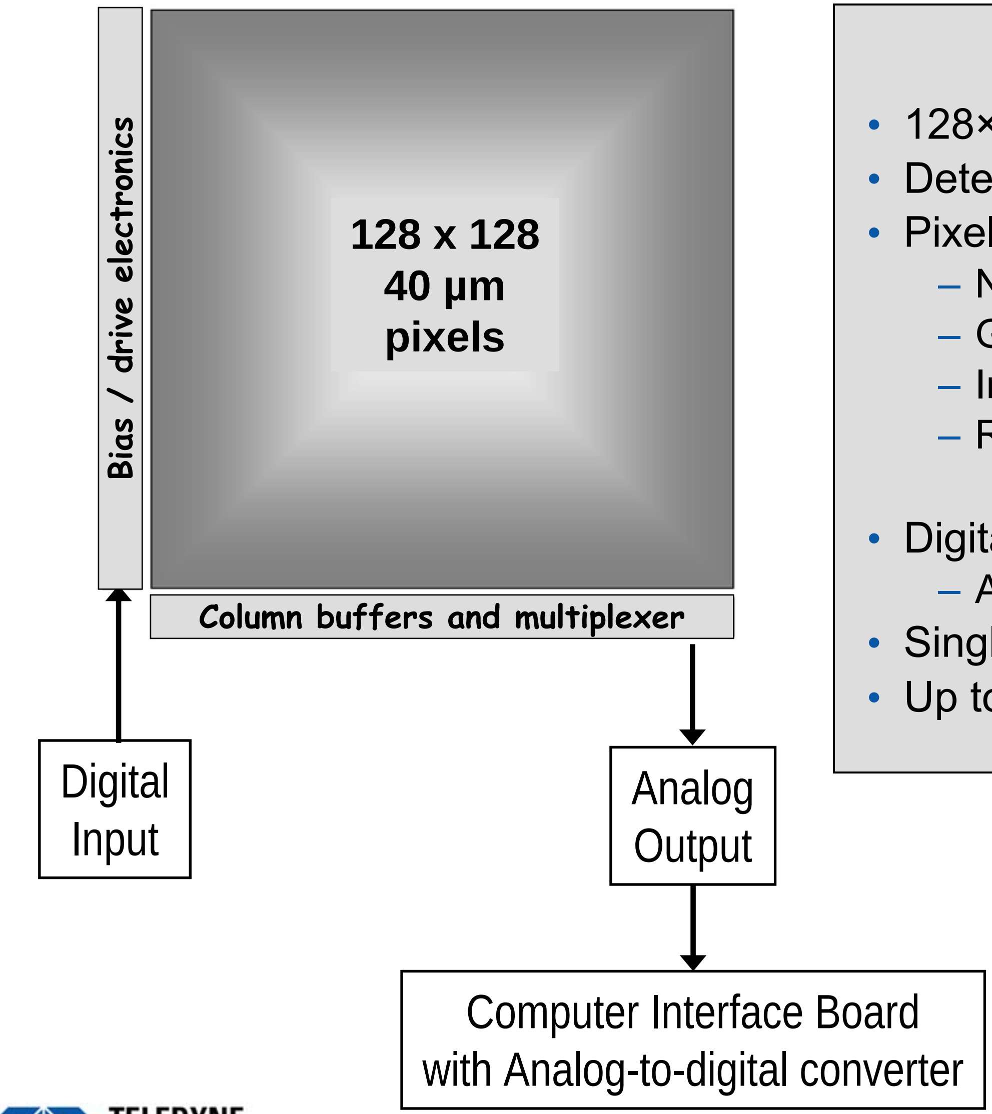
Mars Reconnaissance Orbiter (MRO)



TCM 6604A
640×480 pixels
27 µm pitch
CTIA


TEC Package by Judson

High Speed, Low Noise, Event Driven Readout


Bias / drive electronics

128 x 128
40 µm
pixels

Column buffers and multiplexer

Digital Input

Analog Output

Computer Interface Board
with Analog-to-digital converter

Speedster128

- 128×128 pixels, 40 micron pitch
- Detector material: HgCdTe or Si
- Pixel design
  - Next generation CTIA pixel amplifier
  - Global snapshot, integrate while read
  - In-pixel CDS (correlated double sampling)
  - Readout noise: < 5 e- for HgCdTe
    < 4 e- for Si
- Digital input
  - All clocking produced on-chip
- Single analog output
- Up to 900 Hz frame rate

2008/9: Fabricate and demonstrate
Speedster128 arrays

2009: Modify design for event driven readout

Designed for IR AO and interferometry

High speed, low noise, event driven HyViSI is optimal detector for soft x-ray astronomy

TELEDYNE
IMAGING SENSORS
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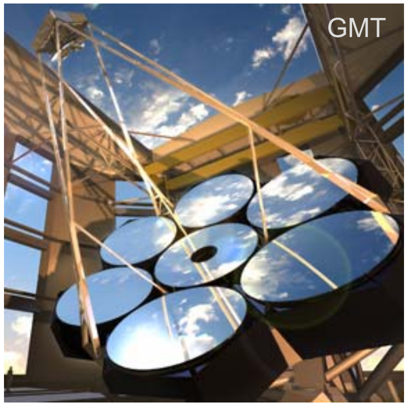
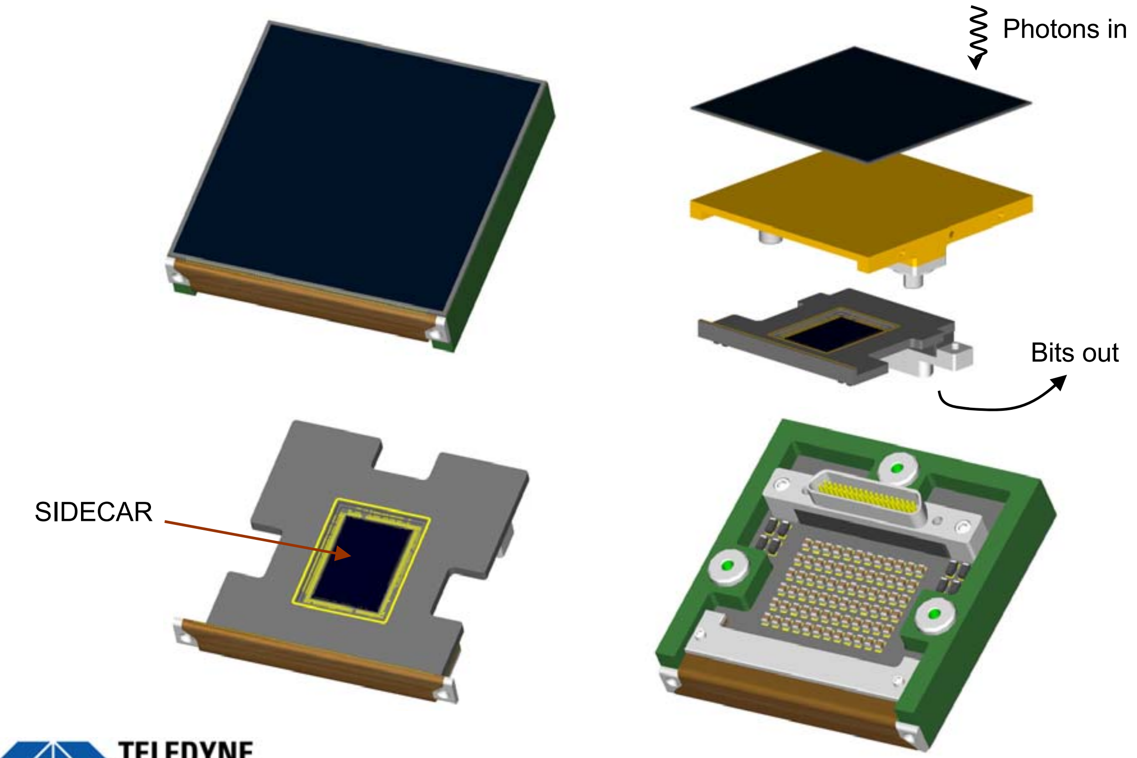
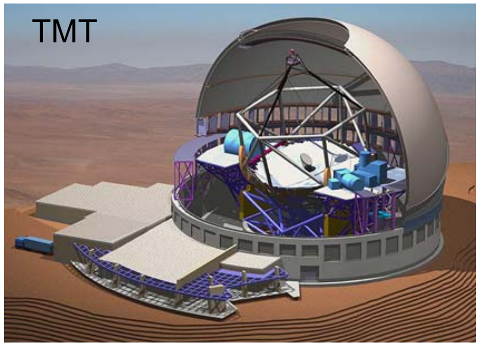
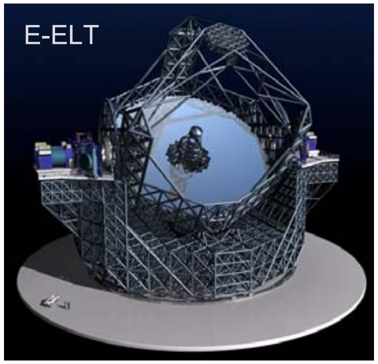
Large IR Astronomy Focal Plane Development
The Next Step: 4096×4096 pixels

- 4096×4096 pixels, 15 µm pitch with embedded SIDECAR ASIC
- Design readout circuit for high yield (4 ROICs per 8-inch wafer)
  - New design process
- Minimize detector cost by growing HgCdTe on silicon substrate
- 4-side buttable for large mosaics
- Option: SIDECAR ASIC integrated into SCA package







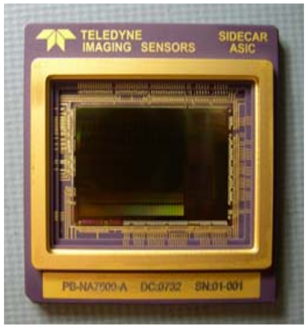


Teledyne – Your Imaging Partner for Astronomy & Civil Space

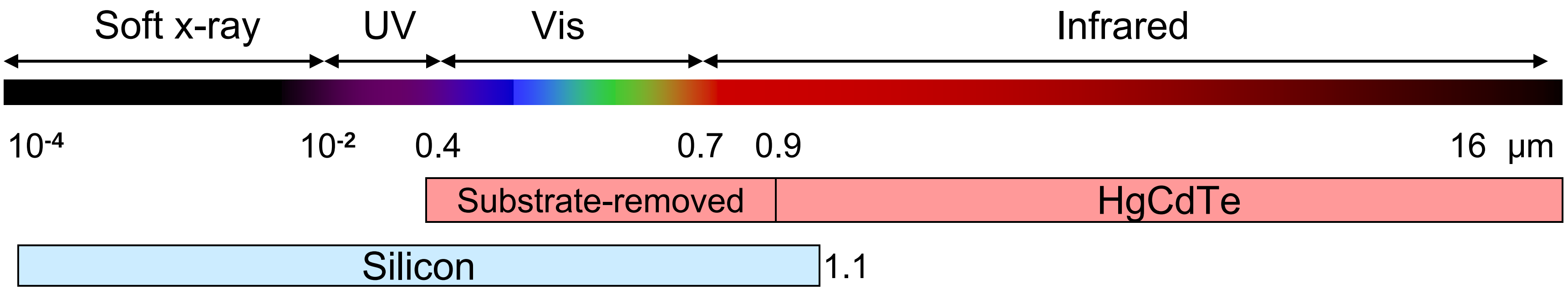
State-of-the-art & high TRL

- CMOS Design
- Detector Materials
- Packaging
- Electronics
- Systems Engineering

Packaging



Electronics



CMOS Design Expertise

- Pixel amplifiers – lowest noise to highest flux
- High level of pixel functionality (LADAR, event driven)
- Large 2-D arrays, pushbroom, redundant pixel design
- Hybrids made with HgCdTe, Si, or InGaAs
- Monolithic CMOS
- Analog-to-digital converters
- Imaging system on a chip
- Specialized ASICs
- Radiation hard
- Very low power